



## Author Index for Volume 6

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- Aboelfotoh, M.O., 1388  
Achete, C.A., 551  
Achtziger, N., 1436  
Aderhold, D., 1587  
Aebi, P., 282  
Afanas'ev, V., 1472  
Aguir, K., 1568  
Agulló-Rueda, F., 1210  
Ahn, J., 48, 1683  
Akaishi, M., 356  
Akkerman, Z., 153  
Ako, F., 847  
Alause, H., 1536  
Albrecht, M., 747, 1467  
Alcubilla, R., 1555  
Aldinger, F., 608  
Alexenko, A.E., 89  
Alkemade, P.F.A., 1726  
Allers, L., 353  
Allon-Alaluf, M., 555  
Alnot, P., 107, 505  
Amaratunga, G.A.J., 207, 700  
Anagnostopoulos, A., 1226, 1494, 1547  
Anderle, M., 559  
Ando, T., 1036, 1753  
Andreyev, A.V., 28  
Androulidaki, M., 1772  
Andújar, J.L., 579, 589, 604, 1550, 1559  
Anghel, L., 1226, 1494, 1547  
Anikin, M., 1249  
Anthony, T.R., 120, 1707  
Apakina, V.N., 564  
Arnault, J.C., 235  
Arnodo, C., 1428, 1508  
Ashfold, M.N.R., 247, 569, 817, 898  
Asif Khan, M., 1536  
Aslam, D.M., 394  
Asmussen, J., 1097  
Aspnes, D.E., 196  
Auer, N., 944  
Avigal, Y., 381, 526  
Awakowicz, P., 1816
- Babaev, V.G., 89, 640  
Babanin, A.I., 1528  
Babina, V.M., 640  
Bacon, D., 687  
Badzian, A., 130  
Baik, Y.-J., 1716  
Bailon, L., 1500  
Bakowski, M., 1476  
Baldwin, S.K. Jr., 202  
Balster, T., 1353  
Bano, E., 1489  
Baral, B., 374, 869
- Baránková, H., 224  
Baranov, A.M., 902, 1106, 1784  
Barbolla, J., 1500  
Bardés, D., 1555  
Bárdóš, L., 224  
Barrat, S., 41  
Barrett, D.L., 1262  
Baruchel, J., 1249  
Bassler, M., 1472  
Bataineh, M.M., 1689  
Batori, V., 645  
Battaile, C.C., 1198  
Bauer-Grosse, E., 41  
Baumann, P.K., 398, 403  
Beardmore, G., 450  
Beccard, R., 1301  
Bechstedt, F., 1346  
Beera, R.A., 430  
Behr, D., 654, 1111  
Beloglazov, A.A., 1650  
Belyavina, N.N., 927  
Ben-Jacob, E., 1868  
Ben el Mekki, M., 1550  
Benko, E., 931, 1192  
Benndorf, C., 533, 964  
Berberich, S., 1306  
Bergman, J.P., 1324  
Berg, S., 224  
Bernard, C., 1249  
Bernhardt, J., 1349  
Berns, D.H., 1883  
Bertran, E., 589, 1559  
Bewick, A., 1135  
Bezhenar, N.P., 927  
Bielanska, E., 931  
Bill, J., 608  
Billon, T., 1226, 1494, 1547  
Blanquet, E., 1249  
Bluet, J.M., 1385, 1463  
Bobrov, K., 736  
Bodganovic, I., 320  
Boettger, E., 298  
Boiko, Y., 860  
Boman, M., 1143  
Bonnot, R., 1463  
Borges, C.F.M., 440  
Borges, C.P., 551  
Borst, T., 329  
Bougdira, J., 107, 505  
Bozeman, S.P., 398, 403  
Bozhko, S.A., 927  
Bozzolo, N., 41  
Bregadze, A.Y., 89  
Bremser, M.D., 191, 196  
Brenn, R., 149, 654  
Breskin, A., 687
- Brierley, C.J., 386  
Britton, D.T., 1777  
Brookes, C.A., 348  
Brown, W.D., 430, 952, 1789  
Bruch, C., 107, 505  
Brumitt, K., 390  
Brunet, F., 774, 778, 843  
Brylinski, C., 1405, 1428, 1508  
Buchkremer-Hermanns, H., 411  
Buckley-Golder, I.M., 344  
Burdina, K.P., 987  
Butler, J.E., 1135, 1198  
Byeli, A.V., 1638
- Cabioch, T., 261  
Calderer, J., 1555  
Calliari, L., 559  
Camassel, J., 1385, 1463, 1772  
Cao, G.Z., 1726  
Cappelli, M.A., 1883  
Cappuccio, G., 807  
Carchano, H., 1568  
Carlsson, J.-O., 1143  
Carlsson, J.O., 85  
Carter, C.H. Jr, 1400  
Cassette, S., 1428  
Chakk, Y., 681  
Chakrabarti, K., 991  
Chakrabarti, R., 991  
Chalker, P.R., 333, 344, 839  
Chan, S.S.M., 333, 374  
Chartier, E., 1508  
Chatei, H., 107, 505  
Chaudhuri, S., 991  
Chechik, R., 687  
Chelnokov, V.E., 1480  
Chen, D., 983  
Cheng, T.S., 1539  
Chen, Q., 1536  
Chen, W.M., 1378, 1381  
Chen, Y., 1799  
Cherian, K.A., 1747  
Chhowalla, M., 207  
Chin, K.K., 940  
Chourou, K., 1249  
Choyke, W.J., 1243, 1333  
Christiansen, K., 1467  
Christiansen, S., 1467  
Cimalla, V., 1311  
Clavaguera-Mora, M.T., 1306  
Clavaguera, N., 1306  
Clement, R.E., 169  
Clough, F.J., 879  
Clyne, T.W., 1612  
Colineau, E., 778

- Collaboration, ISOLDE., 1436  
 Collins, A.T., 516  
 Collins, R.W., 55  
 Comes, F.J., 1587  
 Connell, S.H., 1777  
 Constantinidis, G., 1459  
 Constant, L., 664  
 Contreras, S., 1329  
 Cooper, M.A., 1226, 1494, 1547  
 Corat, E.J., 472, 490, 1172  
 Cordery, A., 537  
 Correig, X., 1555  
 Costa, J., 1559  
 Couto, M.S., 975  
 Cremades, A., 95  
 Croitoru, N., 555, 1152, 1868  
 Cunningham, A.J., 1000
- D'Evelyn, M.P., 511, 791, 812  
 Dalibor, T., 1333, 1396  
 Dandy, D.S., 1759  
 Dannenfeldt, M., 1658  
 Davidson, J.L., 398, 403  
 Davis, R.F., 196, 1282, 1862  
 Davis, T.J., 1062, 1135  
 Da, Y., 673  
 Day, A.R., 325  
 Deák, P., 1633  
 Dedulle, J.M., 1249  
 Deguchi, M., 367  
 Delafond, J., 261  
 Delclos, S., 758  
 De Martino, C., 559  
 Dementjev, A.P., 486  
 Demo, P., 1092  
 Demuynck, L., 235  
 Deneuville, A., 516, 774, 778, 843  
 Dennig, P.A., 1036  
 Der Sahagian, S., 721  
 Devaty, R.P., 1243, 1333  
 Dezauzier, C., 1329  
 Dieguez, I., 41  
 Dimitrakopoulos, G.P., 1362  
 Dluzniewski, M., 721  
 Dmitriev, V.A., 1480, 1524, 1528, 1532  
 Domínguez, M., 1555  
 Donnelly, C.M., 787  
 Donnelly, K., 390  
 Dontas, I., 1424  
 Dorignac, D., 758  
 Dorsch, W., 1269  
 Dowling, D.P., 390  
 Doyle, J.P., 1388  
 Drawl, W., 55  
 Dreher, E., 830, 1129  
 Dub, S.N., 574  
 Dumkum, C., 802  
 Dyakonov, M., 1536
- Ebert, W., 329, 940  
 Ecke, G., 1311  
 Eckstein, R., 1269  
 Edwards, N.V., 196  
 Efimchik, A.A., 1638  
 Egdell, R.G., 874
- Egilsson, T., 1289  
 Egret, S., 879  
 Ehrhardt, H., 255, 621, 645  
 Eichhorn, G., 1311  
 El Felk, Z., 1306  
 Ellison, A., 1272, 1289, 1369  
 el Mekki, M.B., 1772  
 Eloy, R., 390  
 Erler, F., 1414  
 Esteve, J., 579  
 Etsion, I., 381  
 Everitt N.M., 826  
 Evsyukov, S.E., 1743
- Fabis, P.M., 191  
 Falkovsky, L.A., 1385  
 Fanciulli, M., 725  
 Fan, Q.H., 422  
 Fecht, H.J., 308, 344, 839  
 Fedorin, I.A., 640  
 Fedotov, S.A., 1638  
 Feldermann, H., 1129  
 Fernandes, A., 769  
 Ferreira, N.G., 472, 490, 1172  
 Filho, A.P., 1824  
 Filippov, V.B., 1005  
 Fischer, C.G., 1777  
 Fisgeer, B., 526, 736  
 Fisher, D., 146, 1643  
 Fissel, A., 1316  
 Fizzotti, F., 320, 1051  
 Flodström, A., 81  
 Flöter, A., 298  
 Flynn, D., 230  
 Folman, M., 681, 736  
 Fookes, A., 893  
 Foord, J.S., 219, 658, 676, 869, 874  
 Forkel-Wirth, D., 1436  
 Förster, H., 1512  
 Fourches-Coulon, N., 542  
 Fox, N.A., 450, 569, 1135  
 Foxon, C.T., 1539  
 Franceschini, D.F., 551, 631  
 Francois, N., 959  
 Franke, M., 1349  
 Frauenheim, T., 207  
 Freire, F.L., 551  
 Freitag, K., 1436  
 Freudenstein, R., 584  
 Friedbacher, G., 1031  
 Friedrich, M., 33, 612  
 Frischholz, M., 1396, 1485  
 Fuchs, N., 752, 1010  
 Fujimori, N., 1057  
 Fukarek, W., 594  
 Fukui, M., 1  
 Furthmüller, J., 1346  
 Fusco, G., 559, 725, 783
- Galluzzi, F., 361, 712, 1564  
 Gao, Q.J., 1836  
 García, I., 1210  
 Gärtner, H., 149  
 Gat, R., 791  
 Geddes, J., 787
- George, M.A., 398, 403  
 Germi, P., 774  
 Gerstner, E.G., 1622  
 Gheeraert, E., 516, 774, 778, 843  
 Giling, L.J., 1726  
 Gilmore, A., 1062  
 Gimeno, S., 604  
 Giorgis, F., 1606  
 Girshick, S.L., 481  
 Giudice, A.L., 1051  
 Glzman, O., 381, 796, 1847  
 Gluche, P., 329  
 Golding, B., 325  
 Götz, A., 1374, 1420, 1489, 1497  
 Gonon, P., 314, 860  
 González, M., 856  
 González Sirgo, M., 1445  
 Gösele, U., 1365  
 Gouzman, I., 526  
 Gracio, J., 422  
 Grdinaru, G., 1392  
 Grdinaru, S.A., 1392  
 Grant, D.M., 802  
 Grasserbauer, M., 1031  
 Graupner, R., 1358  
 Gray, K.J., 191  
 Griffith, P.W., 822  
 Grillenberger, J., 1436  
 Grill, W., 1587  
 Grögler, T., 1658  
 Gröning, P., 282  
 Gro, S., 1420  
 Gross, M., 1129  
 Grossman, E., 687  
 Gu, C., 673  
 Guillot, G., 1504  
 Gülich, H., 654  
 Guo, W.H., 12  
 Guseva, M.B., 89, 640  
 Gutheit, T., 649  
 Gütler, H., 649
- Hahn, I.T., 959  
 Hahn, J., 612, 1005  
 Hakovirta, M., 694  
 Hallin, C., 1289, 1297, 1369, 1378, 1381, 1485  
 Halperin, G., 381  
 Hammerschmidt, A., 944  
 Hanzawa, H., 1595  
 Hartmann, P., 456, 763  
 Hase, N., 367  
 Hashimoto, M., 1047  
 Hassard, J.F., 353  
 Hatanaka, Y., 1081  
 Hatta, A., 717, 743, 1015, 1041  
 Hattori, R., 884, 889  
 Haubner, R., 240, 286, 406, 456, 494, 763  
 Hayashi, K., 303  
 Hayashi, Y., 1117  
 Heera, V., 1432  
 Heindl, J., 1269  
 Heinz, K., 1349  
 Heissenstein, H., 1440  
 Helbig, R., 1293, 1321, 1440, 1467  
 Hemer, R., 752  
 Henry, A., 1289, 1369

- Herres, N., 654  
 Heszler, P., 85  
 He, Y., 1799  
 Heydemann, V.D., 1262  
 Higuchi, K., 1599  
 Hinneberg, H.-J., 1019  
 Hiraki, A., 717, 743, 1015, 1041  
 Hirakuri, K.K., 1031  
 Hoffman, A., 381, 526, 681, 687, 736, 796,  
     1847  
 Hofmann, D., 1269  
 Hofsäss, H., 830, 1129  
 Hokazono, A., 339, 865  
 Hollering, M., 1358, 1451  
 Holmes, D.S., 308  
 Hong, B., 55  
 Horii, N., 1874  
 Howard, A.S., 353  
 Huang, J.T., 12  
 Huant, S., 1536  
 Hudson, J.B., 511, 791  
 Hudson, M.D., 386  
 Hug, G., 261  
 Hurtós, E., 1306  
 Hwang, J., 12  
 Hylén, A.-L., 1456  
 Hyun, S., 325
- Ibach, H., 1353  
 Ibarra, A., 856  
 Iha, K., 490, 1172  
 Imai, T., 1057  
 Inushima, T., 835, 852  
 Irvine, K.G., 1524  
 Ishikura, T., 339  
 Isoya, J., 99, 356  
 Itoh, A., 1599  
 Itoh, K.-i., 1874  
 Ito, T., 717, 743, 1015, 1041  
 Ivanov, I.G., 1289  
 Iwasaki, Y., 889
- Jackman, R.B., 219, 333, 374, 658, 676, 869,  
     874  
 Jaeger, M.D., 325  
 Jäger, W., 649  
 Jaksic, M., 320  
 Jamieson, D., 314  
 Jamieson, D.N., 860  
 Janowitz, C., 1226, 1494, 1547  
 Janssen, R., 1420  
 Janzén, E., 1266, 1272, 1289, 1297, 1369,  
     1378, 1381, 1456, 1485  
 Jaouen, M., 261  
 Järrendahl, K., 1282  
 Jaussaud, C., 1226, 1494, 1547  
 Jeon, M.H., 743  
 Jian-xia, L., 673  
 Jiang, N., 743, 1041  
 Jin, Z., 673  
 Ji, R., 48  
 Johnson, D.J., 1799  
 Johnson, J.N., 1000  
 Johnson, S.E., 569
- Johnston, C., 333, 344, 839  
 Jürgensen, H., 1301
- Käckell, P., 1346  
 Kaiser, U., 1316  
 Kajimura, K., 303  
 Kalaugher, E., 826  
 Kalinina, E.V., 1528  
 Kalisha, R., 516, 526, 687  
 Kalish, R., 1622  
 Kalomiros, J., 1226, 1494, 1547  
 Kalss, W., 240  
 Kaltenhäuser, M., 1436  
 Kamo, M., 1753  
 Kanda, H., 28, 99, 146, 356, 708, 1643, 1680  
 Kanehara, H., 1722, 1722  
 Kang, W.P., 398, 403  
 Karabutov, A.V., 1650  
 Karakostas, T., 1362  
 Karasawa, S., 835  
 Karuzskii, A.L., 564  
 Kasper, W., 1816  
 Kátai, S., 1633  
 Kato, T., 1595  
 Katsikini, M., 1539  
 Kawarada, H., 277, 339, 865, 1668  
 Kawasaki, S., 889  
 Kelly, T.C., 390  
 Ke, N., 983  
 Kennou, S., 1424  
 Kern, R.S., 1282  
 Kerns, D.V., 398, 403  
 Khanolkar, A.A., 430  
 Kharlashina, N.N., 172  
 Khin, Y.Y., 1015  
 Khomich, A.V., 417  
 Khriachtchev, L.Yu., 694, 1026  
 Khvostov, V.V., 89, 640  
 Kiflawi, I., 146, 1643  
 Kikegawa, T., 1806  
 Kimoto, T., 1276, 1333  
 Kim, S.H., 959  
 Kimura, T., 1047  
 Kitabatake, M., 367  
 Kitagawa, M., 367  
 Kittler, M., 1512  
 Kiyota, H., 1753  
 Klages, C.-P., 293  
 Klibanov, L., 1152, 1868  
 Klose, S., 308, 344, 839  
 Klotzbücher, T., 599  
 Knapper, M.P., 569  
 Knap, W., 1536  
 Knuyt, G., 435, 1092, 1697, 1697  
 Kobashi, K., 266, 272  
 Kogan, M.S., 564  
 Kohly, W., 308  
 Kohn, E., 329, 940  
 Kohzaki, M., 1599  
 Koide, Y., 847  
 Koidl, P., 149, 654, 1111  
 Kola, P.V., 390  
 Kolitsch, A., 594  
 Komarov, S.F., 511, 791  
 Komninou, P., 1362  
 Komori, M., 501
- Kondrashov, P.E., 902, 1784  
 Kono, S., 463  
 Konov, V.I., 417, 1650  
 Konstantinov, A.O., 1297  
 Konwerska-Hrabowska, J., 617  
 Konyashin, I., 608  
 Konyashin, I.Y., 89  
 Kordina, O., 1289, 1297, 1369, 1378, 1381,  
     1485  
 Korony, G., 1392  
 Kotaki, T., 1874  
 Kotera, H., 367  
 Kožíšek, Z., 1092  
 Krannich, G., 1005  
 Kreissig, U., 626  
 Kreutz, E.W., 599  
 Krötz, G., 1338  
 Kruger, C.H., 202, 476  
 Krüger, J.K., 107, 505  
 Krukowski, S., 1515  
 Kuang, Y., 55  
 Kudryavtsev, Y.P., 1743  
 Kühn, M., 626  
 Kulisch, W., 584, 906  
 Kumar, S., 1830  
 Kumazawa, Y., 1057  
 Kuo, K.-P., 1097  
 Kupfer, H., 33  
 Kurz, H., 1374, 1420, 1497  
 Kusakabe, K., 668  
 Küttel, O.M., 282  
 Kuzmik, J., 1459  
 Kuznetsov, N.I., 1528  
 Kvít, A.V., 564
- Labeau, M., 1249  
 Lacerda, M.M., 631  
 Lacher, F., 1111  
 Ladas, S., 1424  
 Lade, R.J., 569  
 Lagrange, J.P., 516, 778  
 Laimer, J., 406  
 Lam, Y.W., 521, 635  
 Lancin, M., 542  
 Lang, A.R., 1226, 1494, 1547  
 Lappalainen, R., 694, 1026, 1207  
 Larson, J.M., 481  
 Lash, A.A., 640  
 Lassagne, P., 1226, 1494, 1547  
 Laufer, S., 1019  
 Lawson, S.C., 99, 1643  
 Lebedev, Y.A., 224  
 Leckey, R.C.G., 1358  
 Lee, C.S., 521, 635  
 Lee, J., 55  
 Lee, J.-J., 511  
 Lee, J.-W., 959  
 Lee, N., 130  
 Lee, S.T., 635  
 Leidich, D., 1365  
 Leite, N.F., 472, 490, 1172  
 Lempert, G.D., 687  
 Le Normand, F., 235, 664  
 Leonhard, C., 1489, 1497  
 Leoni, M., 807  
 Lévéque, G., 1463

- Leycuras, A., 1385, 1857  
 Ley, L., 730, 747, 1358, 1451  
 Liao, X.Z., 521  
 Licht, T., 1436  
 Lifshitz, Y., 687  
 Lindefelt, U., 1289  
 Lindner, J., 1414  
 Lindsay, J.W., 481  
 Lindström, J.L., 1378  
 Linnarsson, M., 1293  
 Lin, Z.D., 1836  
 Lipkin, L.A., 1400  
 Lippold, G., 906, 1587  
 Lisicki, M., 617  
 Li, X., 1117  
 Lloyd, L., 390  
 Loader, C.B., 822  
 Locher, R., 149, 308, 654  
 Loeffler, J., 608  
 Loginova, O.B., 931  
 Loh, K.P., 219, 874  
 Lollman, D., 1568  
 Lorenz, H.P., 6  
 Lossy, R., 1445  
 Lousa, A., 604  
 Lucazeau, E., 843  
 Ludena, G.M.L., 89  
 Luithardt, W., 533  
 Lupich, I.N., 574  
 Lüpke, G., 1374  
 Lu, X., 673  
 Lux, B., 240, 286, 406, 456, 494, 763
- Machet, J., 970  
 Madar, R., 1249, 1369  
 Maeda, H., 668  
 Mahalingam, P., 1759  
 Maillard-Schaller, E., 282  
 Mainwood, A., 353  
 Mainz, B., 1019  
 Maity, A.B., 991  
 Makepeace, A.P.W., 1226, 1494, 1547  
 Malave, A., 906  
 Malhotra, M., 1830  
 Malogolovets, V.G., 574  
 Malov, Y., 1097  
 Malshe, A.P., 430, 952, 1789  
 Mambou, J., 774, 778  
 Mammana, V.P., 1824  
 Manfredotti, C., 320, 1051  
 Mankelevich, Y.A., 1051  
 Mansano, R.D., 1824  
 Marek, T., 1269  
 Marhic, C., 542  
 Marinelli, M., 717  
 Mariootto, G., 631  
 Markiv, V.Ya., 927  
 Marsal, L.F., 1555  
 Marshall, R.D., 374, 676  
 Martineau, P.M., 1226, 1494, 1547  
 Martinu, L., 440  
 Mary, S., 1135  
 Maslyuk, B.A., 574  
 Matsumoto, O., 1874  
 Matsunami, H., 1276, 1333  
 Matsushima, E., 1753
- Mattern, B., 1358  
 Matthée, T., 293  
 Matz, W., 1432  
 Ma, Y., 476  
 May, P.W., 247, 348, 450, 1135  
 McCarty, K.F., 1219  
 McColl, I.R., 802  
 McCulloch, D.G., 1622  
 McCullough, R.W., 787  
 McGrath, J.J., 394  
 McKeag, R.D., 374  
 McKenzie, D.R., 207, 1622  
 Meaden, G., 893, 898  
 Meaden, G.M., 822  
 Medlin, D.L., 1219  
 Meilunas, R.J., 1157  
 Melnik, N.N., 564  
 Melnik, Y., 1524, 1532  
 Mendes de Barros, R.C., 472, 490, 1172  
 Meng, Q., 673  
 Meng, Y., 120  
 Merchant, A.R., 1622  
 Mergens, M., 599  
 Messier, R., 55  
 Mestres, N., 1550  
 Meunier, F., 970  
 Meyer, C., 1374  
 Meykens, K., 435, 1092, 1697, 1697  
 Michelakis, K., 1459  
 Migulin, V.V., 417  
 Mihalcea, C., 906  
 Mikhailuts, E.Y., 1106  
 Milita, S., 1249, 1369  
 Miller, A.J., 386  
 Milne, W.I., 48, 783, 879  
 Milosavljevic, I., 398, 403  
 Mina, G., 559  
 Mirri, K., 320  
 Mita, Y., 1722, 1722  
 Mitchel, W., 1392  
 Mitsuda, Y., 468  
 Mitsuhashi, M., 852  
 Mitura, E., 721  
 Mitura, S., 721  
 Mityagin, Y.A., 564  
 Miyata, K., 266  
 Mizuuchi, Y., 277  
 Moelle, C., 344, 839  
 Moisan, M., 440  
 Mollá, J., 856  
 Möller, W., 594  
 Moll, J.A., 721  
 Moll, J.J., 721  
 Monemar, B., 1378, 1381  
 Montereali, R.M., 1564  
 Morita, Y., 356  
 Mori, Y., 743, 1015  
 Morooka, S., 668  
 Morris, W.G., 791  
 Mounier, E., 1182  
 Mucera, G., 1051  
 Müller, G., 1542  
 Müller, S., 1269  
 Murakami, M., 847  
 Murakami, T., 1668  
 Murakawa, M., 1668
- Murzin, V.N., 564  
 Mutsukura, N., 547
- Nagano, M., 501  
 Nagasawa, H., 277  
 Nakai, H., 1047  
 Nakama, T., 852  
 Nakamura, K., 339, 1668  
 Nakamura, N., 1047  
 Nakanishi, Y., 1081  
 Nakazawa, H., 1680  
 Nam, O.H., 196  
 Naseem, H.A., 430, 952  
 Nassisi, V., 1650  
 Nazaré, M.H., 769  
 Nemanich, R.J., 398, 403  
 Nennewitz, O., 1414  
 Nesládek, M., 435, 704, 1092, 1697, 1697,  
 1726  
 Nesteruk, I.G., 1067  
 Neves, A., 769  
 Nicholson, E., 898  
 Nicholson, E.D., 817, 826, 893  
 Nicholson, J., 898  
 Nickel, K.G., 935  
 Niedzielski, P., 721  
 Niemann, E., 1365  
 Nikitina, I.P., 1524, 1532  
 Nikolaev, A.E., 1532  
 Nilen, R.W.N., 1777  
 Nishimori, T., 463  
 Nishino, S., 1117  
 Nishino, T., 717  
 Nishitani-Gamo, M., 1036  
 Nisida, Y., 1595, 1722, 1722  
 Nistor, L.C., 159  
 Noblanc, O., 1428, 1508  
 Noda, H., 865  
 Noda, S., 1599  
 Nordell, N., 1293, 1388  
 Nöth, H., 286  
 Novikov, N.V., 574  
 Novoselova, E.G., 902, 1784  
 Nugent, K., 314  
 Nyberg, T., 85, 224
- Obermeier, E., 1445, 1448  
 Obraztsova, E.D., 159  
 Obraztsov, A.N., 1124, 1629  
 Oelhafen, P., 830  
 Oesterschulze, E., 906  
 Ogasawara, A., 835  
 Ogawa, T., 1015  
 Ohshima, T., 356  
 Ohya, S., 835  
 Okamoto, M., 1015  
 Oksman, M., 1152  
 Okushi, H., 303, 1124, 1753  
 Oku, T., 847  
 Olejniczak, W., 1081  
 Olszyna, A., 617  
 Opalev, O.A., 426  
 Opyrchal, H., 940  
 Orlikovsky, A.A., 564  
 Otsuki, A., 847

- Ouisse, T., 1226, 1489, 1494, 1547  
 Ovuka, Z., 1476  
 Owano, T.G., 202, 476  
 Ozkan, A.M., 1789
- Pace, E., 361  
 Paderno, Y., 1005  
 Pal, A.K., 991  
 Pallarès, J., 1555  
 Palmour, J.W., 1400  
 Paloura, E.C., 1226, 1494, 1539, 1547  
 Pang, L.Y.S., 333  
 Pan, X.H., 1836  
 Paoletti, A., 717  
 Papaioannou, V., 1362  
 Parikh, N., 196  
 Park, B.S., 1716  
 Park, Y.S., 959  
 Partridge, P.G., 893, 898  
 Pascual, J., 1550, 1772  
 Pauleau, Y., 1182  
 Pauser, H., 406  
 Pavlovsky, I.Y., 1124, 1629  
 Pawłowski, S., 1081  
 Pearce, T., 893  
 Pécz, B., 1297, 1362, 1428  
 Pekko, P., 1207  
 Peng, S., 983  
 Peng, X.F., 1836  
 Peng, X.L., 1612  
 Pensl, G., 1262, 1333, 1396, 1472  
 Peppermüller, C., 1293, 1321, 1440  
 Pereira, E., 422  
 Perestoroin, A.V., 564  
 Pereverteilo, V.M., 931  
 Pernet, M., 774  
 Perry, W.G., 196  
 Petrik, P., 1633  
 Petukhov, M.N., 486  
 Pezoldt, J., 1311, 1414  
 Pfennighaus, K., 1316  
 Phillip, F., 758  
 Philosoph, B., 516  
 Pickard, C.D.O., 1062  
 Pimenov, S.M., 1650  
 Pintaske, R., 1005  
 Pintér, I., 1633  
 Piqueras, J., 95  
 Pirri, C.F., 1606  
 Plass, M.F., 594  
 Plitzko, J., 935  
 Pobol, I.L., 1067  
 Pochet, T., 320  
 Podzyarey, G.A., 574  
 Polesello, P., 320, 1051  
 Polini, R., 235  
 Polo, M.C., 579, 1550  
 Polushin, N.I., 987  
 Polyakov, V.B., 172  
 Polyakov, V.I., 1650  
 Pongratz, P., 752, 763, 1010  
 Pons, M., 1249  
 Poo, T.L., 1683  
 Prater, J.T., 1862  
 Prawer, S., 314, 860, 1622  
 Prieur, E., 1272
- Prince, R.H., 1799  
 Przymusiala, P., 721  
 Quaeyhaegens, C., 435, 1092, 1697, 1697
- Rackaitis, M., 1  
 Radamson, H., 1369  
 Radnóczki, G., 1428  
 Ralchenko, V.G., 159, 417  
 Ramesham, R., 17  
 Räsänen, M., 694, 1026  
 Rats, D., 758  
 Rava, P., 1606  
 Ravindra, N.M., 1157  
 Rawles, R.E., 791  
 Raynaud, C., 1504  
 Reece, D.M., 386  
 Rego, C.A., 247  
 Reichert, W., 1445, 1448  
 Reiß, H., 298  
 Reinhard, D.K., 1689  
 Reinke, S., 584  
 Reislöhner, U., 1436  
 Remeš, Z., 1726  
 Rémy, M., 107, 505  
 Ren, H., 411  
 Richier, C., 1504  
 Richter, F., 612, 626, 1005  
 Richter, V., 516  
 Richter, W., 1316  
 Riley, J.D., 1358  
 Ristein, J., 730  
 Rittmayer, G., 944  
 Rivière, J.P., 261  
 Robert, J.L., 1329  
 Robertson, J., 212, 255, 700, 783, 879  
 Rochotzki, R., 33  
 Rodríguez-Viejo, J., 1306  
 Rodway, D., 658  
 Romanko, L.A., 1674  
 Romanus, H., 1414  
 Ronning, C., 830, 1129  
 Rosa, J., 704, 1092  
 Rose, M.F., 17  
 Rosiwal, S.M., 1658  
 Rösler, M., 935  
 Rosser, K.N., 247, 450, 569  
 Rossi, M., 444  
 Rossi, M.C., 361, 712, 1564  
 Rössler, U., 1342  
 Rottner, K., 1293, 1321, 1396  
 Rottner, K.H., 1485  
 Roumiguières, B., 1568  
 Roy, R., 1747  
 Rüb, M., 1436  
 Rusli F., 700, 1683
- Sachdev, H., 286, 494  
 Sadowski, M.L., 1536  
 Saito, T., 668  
 Sakai, S., 468  
 Sakamoto, H., 463  
 Salvadori, M.C., 1824  
 Salvatori, S., 361, 712, 1564
- Samlenski, R., 149, 654  
 Samokhvalov, N.V., 426  
 Sánchez, G., 579  
 Sánchez Olias, J., 1210  
 Sasaki, T., 743, 1015, 1041  
 Satoh, S., 1841  
 Sato, K., 1753  
 Sato, T., 1806  
 Sato, Y., 99, 1036, 1753  
 Sattel, S., 255  
 Savage, J.A., 386, 658  
 Savage, S.M., 1485  
 Scardi, P., 807  
 Schaaff, P., 1777  
 Schaarschmidt, G., 1019  
 Schaefer, J.A., 1353  
 Schäfer, J., 730  
 Schäfer, L., 293  
 Schardt, J., 1349  
 Scharmann, F., 1311  
 Scharnholz, S., 1497  
 Scheffer, L., 1868  
 Scheibe, H.J., 687  
 Scheib, M., 255, 645  
 Schelz, S., 440  
 Schilling, W., 6  
 Schipanski, D., 1311, 1512  
 Schlapbach, L., 282  
 Schmidt, A., 293  
 Schmidt, I., 964  
 Schmitz, D., 1301  
 Scholz, R., 1365  
 Scholz, W., 906  
 Schöner, A., 1293, 1321, 1388, 1396, 1485  
 Schreck, M., 95, 752, 1010  
 Schröter, B., 1316  
 Schultrich, B., 687  
 Schulze, N., 1262  
 Schulz, G., 649  
 Schwan, J., 645  
 Schwefel, R., 1816  
 Schwierz, F., 1512  
 Seal, M., 975  
 Sebastian, M., 1129  
 Seidman, A., 1152, 1868  
 Sekiguchi, T., 303  
 Sekita, M., 1036  
 Sellschop, J.P.F., 1777  
 Semoto, K., 1047  
 Sendezera, E.J., 1777  
 Sergeichev, K.F., 417  
 Serin, V., 758  
 Sessa, V., 444, 807  
 Sharma, S.N., 1559  
 Shatwell, R.A., 822  
 Shchukarev, A.V., 1528  
 Shechter, H., 736  
 Shefer, E., 687  
 Sheglov, M.P., 1524  
 Shima, S., 367  
 Shimizu, R., 272  
 Shimomura, O., 1806  
 Shimomura, S., 1680  
 Shintani, Y., 266, 272  
 Shiomi, H., 835  
 Shipko, A.A., 1067  
 Shirafuji, J., 884, 889

- Shiraishi, T., 835, 852  
 Shiryaev, A.A., 172  
 Shi, X., 230  
 Shuh, D.K., 1883  
 Sieber, N., 1451  
 Silva, R.F., 769  
 Šimůnek, A., 944  
 Singer, R.F., 1658  
 Singh, M., 1378  
 Singh, R., 1400  
 Siokou, A., 1424  
 Sirineni, G.M.R., 952  
 Sitar, Z., 1862  
 Sittas, G., 146  
 Skierbiszewski, C., 1536  
 Skorupa, W., 1414, 1432, 1445  
 Slater, Jr. D.B., 1400  
 Smirnov, I.S., 902, 1784  
 Smith, F.W., 153  
 Smits, P.C.H.J., 1726  
 Smolin, A.A., 159, 417  
 Snitka, V., 1  
 Sokolowska, A., 721  
 Somma, F., 1564  
 Son, N.T., 1378, 1381  
 Sörman, E., 1378, 1381  
 Souw, E.-K., 1157  
 Spaeth, C., 626  
 Speisser, C., 235  
 Spie, L., 1414  
 Sridhara, S., 1333  
 Srolovitz, D.J., 1198  
 Stals, L.M., 435, 704, 1092, 1697, 1697  
 Stammler, M., 747  
 Stampfl, A.P.J., 1358  
 Stanishevsky, A., 721  
 Stanishevsky, A.V., 1026  
 Starke, U., 1349  
 Staryga, E., 721  
 Stauden, T., 1311  
 Steeds, J.W., 1062, 1135  
 Stefanov, E., 1500  
 Stein von Kamienski, E., 1374, 1420  
 Stein Von Kamienski, E.G., 1489, 1497  
 Stenberg, G., 1143  
 Stöckel, R., 747  
 Stoemenos, J., 1306, 1362, 1448, 1772  
 Stokes, E.B., 511  
 Störi, H., 406  
 Strauch, G., 1301  
 Strausser, Y.E., 55  
 Strel'nitskij, V.E., 426  
 Stritzker, B., 752, 1010  
 Strunk, H.P., 747, 1269, 1467  
 Sudarshan, T.S., 1392  
 Suetin, N.V., 1051  
 Sugino, T., 884, 889  
 Sumiya, H., 1841  
 Sun, Y., 230  
 Sun, Z., 230  
 Suvorov, A.V., 1400  
 Suzuki, N., 1874  
 Svensson, B.G., 1388  
 Sychov, I.A., 417  
 Syrkin, A.L., 1463, 1480  
 Syyväjärvi, M., 1266, 1456  
 Szeles, C., 1157  
 Szilágyi, E., 1633  
 Szmidt, J., 721  
 Szűcs, F., 344, 839  
 Tachibana, T., 266, 272  
 Tadic, T., 320  
 Tagliaferro, A., 559, 725, 783  
 Takai, Y., 272  
 Takakuwa, Y., 463  
 Takeuchi, S., 1668  
 Tanabe, K., 1057  
 Tanaka, J., 1753  
 Tanaka, S., 1282  
 Taniguchi, T., 1806  
 Tarutani, M., 272  
 Tass, Z., 255  
 Tautz, F.S., 1353  
 Tay, B.K., 230  
 te Nijenhuis, J., 1726  
 Tereshin, A.A., 1097  
 Terranova, M.L., 444, 807  
 Theel, T., 645  
 Therin, M., 390  
 Theys, B., 1226, 1494, 1547  
 Thiele, J.-U., 830  
 Thomas, P., 1329  
 Thompson, D.J., 676  
 Thorpe, M.F., 325  
 Thürer, K.-H., 1010  
 Timoshenko, V.Y., 1629  
 Tkachenko, S.D., 564  
 Toda, N., 1841  
 Tong, F.-M., 1157  
 Tong Lee, S., 521  
 Tracey, S., 676  
 Trava-Airoldi, V.J., 472, 490, 1172  
 Tresso, E., 1606  
 Tsang, R.S., 247  
 Tsong, T.T., 55  
 Tsui, Y.C., 1612  
 Tsuno, T., 1057  
 Tsuruga, S., 668  
 Tucciarone, A., 717  
 Tuominen, M., 1272, 1369, 1456  
 Tuomi, T., 1272, 1369  
 Turban, G., 542  
 Ubhi, H.S., 822  
 Uchida, K., 1599  
 Uhlig, H., 608  
 Uhrmacher, M., 1436  
 Ulcinas, A., 1  
 Ulrich, S., 621, 645  
 Urasaki, T., 501  
 Urban, K., 649  
 Utsch, J., 411  
 Utsumi, W., 1806  
 Uzan-Saguy, C., 516  
 Vackář, J., 944  
 Vandebulcke, L., 758  
 Vandevalde, T., 435  
 Vanček, M., 704, 1092  
 van Enckevort, W.J.P., 975, 1726  
 Van Landuyt, J., 159  
 Vanzetti, L., 559  
 Vasquez, S., 551  
 Vázquez, A.J., 1210  
 Vehanen, A., 1272  
 Verdonck, P., 1824  
 Verhoeven, H., 298  
 Vescan, A., 329  
 Viera, G., 1559  
 Vila, R., 856  
 Vittone, E., 320, 1051  
 Vlasov, I.I., 417  
 Voellmar, S., 687  
 Volchkov, N.A., 564  
 Volkov, Y.Y., 426  
 Vorlíček, V., 704  
 Voronina, S.V., 417  
 Voronkin, M.A., 574  
 Wächter, R., 537  
 Wagner, C., 1338  
 Wahl, E.H., 476  
 Wakiyama, K., 501  
 Wang, L.C., 743  
 Wang, W.L., 579  
 Wang, W.N., 569, 1062, 1135  
 Wang, X., 230  
 Ward, B.L., 398, 403  
 Watanabe, H., 303, 1124  
 Watanabe, K., 99, 708, 1036  
 Watanabe, T., 852  
 Weeks, J.R., 817  
 Wei, A., 983  
 Weill, N., 390  
 Weishart, H., 1414, 1432  
 Weiss, H., 411  
 Wellenhofer, G., 1342  
 Welzel, T., 33  
 Werder, M., 1816  
 Werner, M., 308, 344, 839  
 Werninghaus, T., 612, 1019  
 Wesner, D.A., 599  
 White, M., 394  
 Whitfield, M.D., 658, 676  
 Wickramanayaka, S., 1081  
 Widmayer, P., 621  
 Wiech, G., 944  
 Wiescher, D., 255  
 Wild, C., 1111  
 Winnacker, A., 1269  
 Wisbey, A., 822, 898  
 Wischmeyer, F., 1365  
 Witthuhn, W., 1436  
 Wittig, J., 398, 403  
 Wittorf, D., 649  
 Woelk, E.G., 1301  
 Wolden, C.A., 1862  
 Wolter, S.D., 1747  
 Wong, K.W., 635  
 Wong, S.P., 983  
 Won, J., 1041  
 Won, J.H., 743  
 Woo, H.K., 635  
 Wróbel, A.M., 1081  
 Wurzinger, P., 752, 763

- Xiu-di, S., 673  
Yablokov, S.Y., 1784  
Yagi, H., 1041  
Yakimova, R., 1266, 1272, 1369, 1456  
Yamamoto, K., 1036  
Yamamoto, Y., 1057  
Yamanaka, S., 303  
Yamashita, S., 339, 1668  
Yang, B.X., 153  
Yang, G.S., 394  
Yang, H., 1683  
Yin, Y., 207  
Yin, Z., 153  
Yokoba, M., 847  
Yokota, Y., 266  
Yoon, S.F., 48, 1683  
Yoshida, K.-i., 547  
Yoshii, M., 1031  
You, L.P., 1836  
Younes, C.M., 450  
Young, J., 1536  
Yugo, S., 1047  
Yun, W.S., 959  
Yu, Z., 81  
Zachai, R., 298, 649  
Zahn, D.R.T., 33, 612, 1019  
Zak, J., 721  
Zalicki, P., 476  
Zanghellini, E., 551  
Zare, R.N., 476  
Zarrabian, M., 542  
Zeiler, E., 1658  
Zekentes, K., 1362, 1772  
Zgonc, K., 812  
Zhang, F., 1836  
Zhang, L.Y., 348  
Zhang, Q., 1683  
Zhang, R.J., 521  
Zhang, R.Q., 589, 1559  
Zhang, Y., 635  
Zhao, M., 202  
Zheleva, T., 196  
Zheng, Z., 230  
Zhong-de, X., 673  
Zhou, G., 272  
Zhuk, A.Z., 640  
Ziegler, A., 1358  
Ziemann, P., 621  
Zou, G., 673  
Zukauskas, D., 1

## Subject Index

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**a-Axis**

High quality 4H-SiC grown on various substrate orientations, 1289

**a-C/a-C:H thin films**

Insight on the microscopical structure of a-C and a-C:H thin films through electron spin resonance analysis, 725

**A-C:H**

Formation of nanocrystalline diamond by hydrocarbon plasma beam deposition, 255

**a-C:H**

Improvement of mechanical properties of a-C:H by silicon addition, 559

Transition from polymer-like to diamond-like a-C:H films. Structure and mechanical properties, 574

Photoluminescence in hydrogenated amorphous Carbon, 700

Diamond-like carbon metal–semiconductor–metal switches for active matrix displays, 879

**A-SiC**

Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226

Low frequency noise in silicon carbide Schottky diodes, 1494

Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547

**Absorption**

Spatially resolved measurements of absolute CH<sub>3</sub> concentration in a hot-filament reactor, 476

Optical properties of diamond film deposited by CVD of Freon: studies on mechanical properties from the absorption band tail, 991

**ac Conduction**

An impedance spectroscopy investigation of polycrystalline diamond from dc to 1 GHz, 1689

**Acetylene**

Low-temperature deposition of optically transparent diamond using a low-pressure flat flame, 1862

**A.C. impedance**

Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17

**Actinometry**

H actinometry with CF<sub>4</sub> addition in microwave plasma-assisted chemical vapor deposition of diamond, 472

**Activation energy**

The activation energy for diamond growth from CCl<sub>4</sub>/H<sub>2</sub> mixtures in a hot-filament reactor, 1172

**Adhesion**

Microtribological properties of diamond-like and hydrogenated carbon coatings grown by different methods, 1

Single source deposition of Me-C:H films using metal-organic precursors, 533

Stiffness, residual stresses and interfacial fracture energy of diamond films on titanium, 1612

**Adhesion strength**

Evaluation of MPCVD diamond film adhesion on hard metal substrates by micro Raman spectroscopy, 769

**Adsorption abstraction of Chlorine**

Deposition of diamond from plasma jets with chlorobenzenes as carbon source, 1874

**AFM**

Comparison of the surface structure of carbon films deposited by different methods, 721

**Aggregation rate**

The aggregation of nitrogen and the formation of A centres in diamonds, 1643

**Al-, B-doping**

Hydrogen incorporation in epitaxial layers of 4H- and 6H-silicon carbide grown by vapor phase epitaxy, 1293

**Al/boron-doped polycrystalline diamond**

Hysteresis loop in the current–voltage characteristic of Al/boron-doped polycrystalline diamond Schottky contact, 12

**AlGaN epitaxy**

Growth, doping and characterization of Al<sub>x</sub>Ga<sub>1-x</sub>N thin film alloys on 6H-SiC(0001) substrates, 196

**Alloy**

Growth, doping and characterization of Al<sub>x</sub>Ga<sub>1-x</sub>N thin film alloys on 6H-SiC(0001) substrates, 196

**AlN thin film**

Growth of AlN thin films on (111) and (100) silicon by pulsed laser deposition in nitrogen plasma ambient, 1015

**Aluminium nitride**

X-ray diffraction analysis of aluminum nitride sintered with cubic boron nitride, 927

**Aluminum nitride**

Growth and doping via gas-source molecular beam epitaxy of SiC and SiC/AlN heterostructures and their microstructural and electrical characterization, 1282

**Amorphous**

Nitrogen and iodine doping in amorphous diamond-like carbon films, 555

**Amorphous carbon**

AES and XPS observations of HFCVD diamond deposition on monocrystalline (111) copper, 664

Chemical vapour deposition of hard a-C:H films from CH<sub>2</sub>I<sub>2</sub>, 1143

Mechanisms of intrinsic stress generation in amorphous carbon thin films prepared by magnetron sputtering, 1182

DLC growth by ion beam assisted deposition: a molecular simulation, 1638

Influence of substrate temperature and microwave power on the properties of a-C:H films prepared using the ECR-CVD method, 1683

**Amorphous carbon films**

Comparison of the surface structure of carbon films deposited by different methods, 721

**Amorphous hydrogen-free diamond-like carbon**

Raman diagnostics of amorphous diamond-like carbon films produced with a mass-separated ion beam, 694

**Amorphous hydrogenated carbon**

Single source deposition of Me-C:H films using metal-organic precursors, 533

- Structure and properties of a-C:H films deposited onto polymeric substrates, 551
- Hard a-C(N):H films obtained from plasma decomposition of methylamine-containing mixtures, 631
- Diamond-like hydrogenated amorphous carbon films studied by X-ray emission spectroscopy, 944
- A factorial analysis of the preparation and properties of a-C:H thin films, 1000
- Amorphous III-V semiconductors
- Amorphous GaAs<sub>1-x</sub>N<sub>x</sub> thin films on crystalline Si substrates: growth and characterizations, 1568
- Amorphous semi-conductors
- Colour sensing applications of hydrogenated amorphous silicon carbide, 1542
- Amorphous silicon–carbon alloys
- Electrical properties of PECVD amorphous silicon–carbon alloys from amorphous–crystalline heterojunctions, 1555
- Annealing
- The irradiation and annealing of Si-doped diamond single crystals, 146
  - A two-step process for the formation of a Mo<sub>2</sub>C contact on polycrystalline diamond films, 843
- Application
- Use of diamond-like carbon films in X-ray optics, 902
- Applications
- Diamond coatings for IR window applications, 386
  - Electrical conduction in polycrystalline diamond and the effects of UV irradiation, 860
  - Diamond-like carbon metal–semiconductor–metal switches for active matrix displays, 879
  - Tetrahedral amorphous carbon (ta-C) coatings for processing tools to reduce contamination in the analysis of trace elements, 1207
- Arcjet PECVD
- Near-edge X-ray absorption fine structure spectroscopy of arcjet-deposited cubic boron nitride, 1883
- Argon–silane atmosphere
- Improvement of mechanical properties of a-C:H by silicon addition, 559
- Atomic force microscopy
- Microtribological properties of diamond-like and hydrogenated carbon coatings grown by different methods, 1
  - Surface characterization of smooth heteroepitaxial diamond layers on  $\beta$ -SiC (001), 277
  - Kinetics of the initial stages of CVD diamond growth on non-diamond substrates: surface catalytic effects and homoepitaxy, 681
  - Friction tracks on diamond surfaces imaged by atomic force microscopy, 975
  - Aluminium implantation of *p*-SiC for ohmic contacts, 1414
  - Influence of nitrogen doping on photoconductivity properties of a: DLC films, 1868
- Atomic hydrogen
- Enhanced deposition rate of diamond in atmospheric pressure plasma CVD: effects of a secondary discharge, 202
  - Effects of electron and atomic hydrogen irradiation on gas-source molecular beam epitaxy of diamond with pure methane, 463
  - Atomic hydrogen-induced chemical vapor deposition of a-Si:C:H thin-film materials from alkylsilane precursors, 1081
- Atomic structure
- Investigation of modified 3C SiC(100) surfaces by surface-sensitive techniques, 1353
- Au
- Diamond deposition on noble metals, 240
- Austenitic stainless steel
- Evaluation of diamond-like carbon-coated orthopaedic implants, 390
- Band bending
- Electronic and structural properties of the interface between c-Si(111) and diamond-like carbon, 730
- Band offset
- Electronic and structural properties of the interface between c-Si(111) and diamond-like carbon, 730
- Band structure
- Capacitance–voltage measurements on metal–SiO<sub>2</sub>–boron-doped homoepitaxial diamond, 852
  - Tuning the electron affinity of CVD diamond with adsorbed caesium and oxygen layers, 874
  - Photoconductivity of CVD diamond under bandgap and subbandgap irradiations, 1157
  - Progress in the study of optical and related properties of SiC since 1992, 1243
- Beam-induced current (EBIC)
- Electron beam-induced current imaging of chemical vapor-deposited diamond films, 95
- Bending
- Wafer warpage, crystal bending and interface properties of 4H-SiC epi-wafers, 1369
- Bias
- Enhanced deposition rate of diamond in atmospheric pressure plasma CVD: effects of a secondary discharge, 202
  - Nucleation and initial growth of bias-assisted HFCVD diamond on boron nitride films, 579
  - Biased enhanced nucleation of diamond on metals: an OES and electrical investigation, 658
  - Growth and defects of diamond facets under negative biasing conditions in a microwave plasma CVD process, 1010
  - Formation mechanisms of diamond precursors during the nucleation process, 1047
  - In-situ ellipsometry study of initial stage of bias-enhanced nucleation and heteroepitaxy of diamond on silicon(100) by hot filament chemical vapor deposition, 1117
- Bias-enhanced nucleation
- Influence of process parameters on the size of the bias-nucleated area for diamond deposition with plasma-enhanced chemical vapour deposition, 6
  - The chemical nature of the carbon precursor in bias-enhanced nucleation of CVD diamond, 526
- Bias enhanced nucleation
- Optimising control of microwave plasma bias enhanced nucleation for heteroepitaxial chemical vapour deposition diamond, 676
- Bidimensional electron gas
- Contactless characterisation of 2D-electrons in GaN/AlGaN HFETs, 1536
- BN films
- Optical study of boron nitride thin films prepared by plasma-enhanced chemical vapor deposition, 1550
- BN phases
- Growth and characterisation of boron nitride films: layer sequence and phase identification, 594
- Bonded SOI
- $\beta$ -SiC films on SOI substrates for high temperature applications, 1448
- Boron
- Formation of cubic boron nitride thin films by reactive cathodic arc evaporation, 1005
  - Electron field emission from thin fine-grained CVD diamond films, 1111
  - Hydrogen-, boron-, and hydrogen-boron-related low temperature photoluminescence of 6H-SiC, 1321
- Boron-doped homoepitaxial diamond
- Optical and electrical investigation of boron-doped homoepitaxial diamond, 835

- Boron carbide substrates**  
Deposition of CVD diamond onto boron carbide substrates, 450
- Boron doping**  
Phosphorescence in high-pressure synthetic diamond, 99  
High-voltage Schottky diode on epitaxial diamond layer, 329  
Effects of simultaneous boron and nitrogen addition on hot-filament CVD diamond growth, 456  
The influence of boron doping on the structure and characteristics of diamond thin films, 521  
Investigation of the boron incorporation in polycrystalline CVD diamond films by TEM, EELS and Raman spectroscopy, 763  
Effect of boron incorporation on the structure of polycrystalline diamond films, 774  
Minimization of the defects concentration from boron incorporation in polycrystalline diamond films, 778  
The optical characterization of boron-doped MPCVD diamond films, 940  
Field-emission studies of boron-doped CVD diamond films following surface treatments, 1135
- Boron nitride**  
Nucleation and initial growth of bias-assisted HFCVD diamond on boron nitride films, 579  
Modeling interface structures of cubic boron nitride films deposited heteroepitaxially and via a hexagonal boron nitride interlayer on silicon (001) surfaces, 589  
Molecular structure of E-BN, 617  
Investigation of contact phenomena at cubic boron nitride–filler metal interface during electron beam brazing, 1067  
How plastic deformation can produce texture in graphitic films of boron nitride, carbon nitride, and carbon, 1219
- Breakdown voltage**  
Numerical study of avalanche breakdown of 6H-SiC planar *p-n* junctions, 1500
- Buffer layer**  
Microstructure and growth of MWCVD diamond on  $\text{Si}_{1-x}\text{C}_x$  buffer layers, 649  
Residual strains in GaN grown on 6H-SiC, 1524  
A study of the initial stages of diamond deposition on ferrous substrates coated by a nitrided chromium interlayer and on nitrided polycrystalline chromium substrates, 1847
- Bulk diamond**  
Investigation of lattice impurities and photochromic centres in diamond with high resolution positron annihilation spectroscopy, 1777
- 3C SiC**  
Optical monitoring of the growth of 3C SiC on Si in a CVD reactor, 1857
- c-Axis**  
High quality 4H-SiC grown on various substrate orientations, 1289
- C-BN**  
Investigation of the c-BN/h-BN phase transformation at normal pressure, 286
- $^{13}\text{C}$ -diamond**  
Thermodynamic properties of  $^{13}\text{C}$ -diamond, 172
- c-Si:C:H interface**  
Electronic and structural properties of the interface between c-Si(111) and diamond-like carbon, 730
- 3C-SiC heteroepitaxy**  
Optical investigation of thick 3C-SiC layers deposited on bulk silicon by CVD, 1385
- C/Si ratio dependence**  
Surface polarity dependence in step-controlled epitaxy: progress in SiC epitaxy, 1276
- $\text{C}_3\text{N}_4$**   
Preparation of  $\text{CN}_x$  films by ion beam assisted filtered cathodic arc deposition, 626
- Capture**  
Hysteresis loop in the current–voltage characteristic of Al/boron-doped polycrystalline diamond Schottky contact, 12
- Carbon**  
Chemical vapour deposition of hard a-C:H films from  $\text{CH}_2\text{I}_2$ , 1143  
Oriented diamond growth on platinum via a metal–carbon–hydrogen low-pressure processing route, 1747
- Carbon cluster model**  
“Carbon cluster model” for electronic states at  $\text{SiC}/\text{SiO}_2$  interfaces, 1472
- Carbon film**  
On correlation between the shape of Raman spectra and short-range order structure of hydrogen-free amorphous carbon films, 1026
- Carbon films**  
Boronated tetrahedral amorphous carbon (ta-C:B), 207  
Spontaneous radiation in short period superlattices on the basis of carbon multilayer heterostructures, 1106
- Carbonization**  
Micropipe defects and voids at  $\beta\text{-SiC}/\text{Si}(100)$  interfaces, 1365  
Optical monitoring of the growth of 3C SiC on Si in a CVD reactor, 1857
- Carbonization of SiC layers**  
Infra-red characterization of carbonization of Si surfaces by gas source molecular beam epitaxy, 1772
- Carbon nitride**  
How plastic deformation can produce texture in graphitic films of boron nitride, carbon nitride, and carbon, 1219  
Deposition of carbon nitride via hot filament assisted CVD and pulsed laser deposition, 1799
- Carbonyl**  
Effects of  $\text{Mo}(\text{CO})_6$  and  $\text{W}(\text{CO})_6$  introduced to plasma on diamond synthesis by microwave plasma CVD, 501
- Carbyne**  
The formation of diamond from carbynoid material at ambient pressure, 1743
- Carrier/doping concentration**  
The diamond Irvin curve, 308
- Carrier concentration**  
Optical and electrical investigation of boron-doped homoepitaxial diamond, 835
- Carrier recombination**  
Electron beam-induced current imaging of chemical vapor-deposited diamond films, 95
- Carrier density of p SiC**  
Valence band dispersion of hexagonal SiC, 1342
- Cathodoluminescence**  
Distribution of the cobalt-related luminescence center in HPHT diamond, 708  
Cathodoluminescence spectroscopy of synthetic diamond films, 717  
Growth of AlN thin films on (111) and (100) silicon by pulsed laser deposition in nitrogen plasma ambient, 1015  
Effects of remote hydrogen plasma treatment (RHPT) on ion-implanted CVD diamond, 1041  
Calculation of the stress in large square facets of MPCVD grown diamond from cathodoluminescence and raman spectroscopy measurements and comparison to stress predicted from finite element models, 1062
- Cathodoluminescence (CL)**  
Electron beam-induced current imaging of chemical vapor-deposited diamond films, 95

- Cathodoluminescence spectroscopy**  
 Incorporation of lithium in single crystal diamond: diffusion profiles and optical and electrical properties, 1726
- cBN**  
 Near-edge X-ray absorption fine structure spectroscopy of arcjet-deposited cubic boron nitride, 1883
- Chamber flame method**  
 Comparative study of excitonic recombination radiation from diamonds grown by CVD and HP/HT methods, 1668
- Characterization**  
 Characterization and optimization of mid-frequency plasma-enhanced chemical vapour deposited carbon films using response surface methodology, 537  
 Studies of nanoscale structure and its transformation in pulsed-laser deposited dense diamond-like carbon films, 564  
 Chemical vapour deposition of hard a-C:H films from CH<sub>2</sub>I<sub>2</sub>, 1143
- Chemical**  
 Preferential etching of SiC crystals, 1456
- Chemical bonding**  
 Investigation of modified 3C SiC(100) surfaces by surface-sensitive techniques, 1353
- Chemical vapor deposition**  
 High quality diamond films on WC-Co surfaces, 89  
 Hydrogen-related gap states in the near surface of chemical vapor deposited homoepitaxial diamond films, 303  
 Piezoresistive property of CVD diamond films, 367  
 Effects of electron and atomic hydrogen irradiation on gas-source molecular beam epitaxy of diamond with pure methane, 463  
 Single source deposition of Me-C:H films using metal-organic precursors, 533  
 PACVD nano-crystalline B-C-N thin films obtained by use of an organoboron precursor, 608
- Chemical vapour deposition**  
 Characterization and optimization of mid-frequency plasma-enhanced chemical vapour deposited carbon films using response surface methodology, 537  
 Investigation of the nucleation layer in c-BN film growth, 584  
 Diamond nucleation on silicon during bias treatment in chemical vapour deposition as analysed by electron microscopy, 747  
 Effect of substrate on the characteristics of the interface between diamond film and substrate, 959  
 A factorial analysis of the preparation and properties of a-C:H thin films, 1000  
 Chemical vapour deposition of hard a-C:H films from CH<sub>2</sub>I<sub>2</sub>, 1143  
 Influence of substrate temperature and microwave power on the properties of a-C:H films prepared using the ECR-CVD method, 1683  
 On the {111} penetration twin density in CVD diamond films, 1697  
 Nucleation enhancement behavior of diamond on Si substrate according to surface treatment materials, 1716
- Chlorobenzenes**  
 Deposition of diamond from plasma jets with chlorobenzenes as carbon source, 1874
- Chromium nitride-coated steel substrate**  
 [100]-Textured diamond films for tribological applications, 381
- CMOS**  
 SiC device technology: remaining issues, 1400
- Coating**  
 Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17  
 Insulating diamond coatings on tungsten electrodes, 293
- Colour centre**  
 Measurement of decay time for the NV centre in Ib diamond with a picosecond laser pulse, 1595
- Colour sensors**  
 Colour sensing applications of hydrogenated amorphous silicon carbide, 1542
- Combustion synthesis**  
 Low-temperature deposition of optically transparent diamond using a low-pressure flat flame, 1862
- Composite**  
 The effect of varying deposition conditions on the Young's modulus of diamond coated wires, 817
- Composites**  
 Diamond fibre metal matrix composites, 898  
 CBN-TiH<sub>2</sub> composites: chemical equilibria, microstructure and mechanical studies, 1192
- Computer simulation**  
 Internal field emission at metal/diamond contact and performance of thin film field emitters: computer simulation, 884  
 Morphologies of diamond films from atomic-scale simulations of chemical vapor deposition, 1198
- Computer simulations**  
 Diamond growth chemistry: its observation using real time in situ molecular beam scattering techniques, 219
- Contact**  
 Internal field emission at metal/diamond contact and performance of thin film field emitters: computer simulation, 884
- Contactless characterisation**  
 Contactless characterisation of 2D-electrons in GaN/AlGaN HFETs, 1536
- Contact phenomena**  
 Investigation of contact phenomena at cubic boron nitride-filler metal interface during electron beam brazing, 1067
- Conventional TEM**  
 Crystalline quality of highly oriented diamond films grown on <100> silicon studied by conventional TEM, 41
- Copper**  
 AES and XPS observations of HFCVD diamond deposition on monocrystalline (111) copper, 664
- Copper substrate**  
 Free-standing diamond film preparation using copper substrate, 422
- Cross-sectional Raman spectroscopy**  
 Diamond growth in and above trenches in silicon, 1019
- Crystal growth**  
 Pressure Dependence of Growth Mode of HFCVD Diamond, 81  
 Surface characterization of smooth heteroepitaxial diamond layers on β-SiC (001), 277  
 Cathodoluminescence spectroscopy of synthetic diamond films, 717  
 Minimization of the defects concentration from boron incorporation in polycrystalline diamond films, 778  
 Cubic boron nitride synthesis by pyrolysis of certain polyammoniates of boron hydrides of metals at high pressure, 987  
 Thermodynamics and high-Pressure growth of (Al, Ga, In)N single crystals, 1515
- Crystalline carbon nitride**  
 Preparation of crystalline carbon nitride films on silicon substrate by chemical vapor deposition, 635
- Crystalline quality**  
 Crystalline quality of highly oriented diamond films grown on <100> silicon studied by conventional TEM, 41  
 Lift-off-technique of single-crystal diamond plates: study of the lattice damage of the implanted substrates and the crystalline quality of the homoepitaxial films by ion channelling, 149
- Crystal potential**  
 Shock-wave-induced phase transition in C:N films, 640

- Cubic boron**
- Formation of cubic boron nitride thin films by reactive cathodic arc evaporation, 1005
- Cubic boron nitride**
- Investigation of the nucleation layer in c-BN film growth, 584
  - C-BN thin film formation in a hybrid r.f.-PLD technique, 599
  - PACVD nano-crystalline B-C-N thin films obtained by use of an organoboron precursor, 608
  - Raman spectroscopy investigation of cubic boron nitride single crystals and layers on Si(100), 612
  - Phase stability and stress relaxation effects of cubic boron nitride thin films under 350 keV ion irradiation, 621
  - Elastic properties of polycrystalline cubic boron nitride and diamond by dynamic resonance measurements, 812
  - X-ray diffraction analysis of aluminum nitride sintered with cubic boron nitride, 927
  - Formation peculiarities of the interfacial structure during cBN wetting with Ag-Ti, Ag-Zr and Ag-Hf alloys, 931
  - Cubic boron nitride synthesis by pyrolysis of certain polyammoniates of boron hydrides of metals at high pressure, 987
  - Electrical properties and thermal stability of ion beam deposited BN thin films, 1129
  - CBN-TiH<sub>2</sub> composites: chemical equilibria, microstructure and mechanical studies, 1192
- Cubic polytypes**
- Identification of the cubic and hexagonal polytypes of GaN with X-ray absorption measurements, 1539
- CVD**
- Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17
  - Pressure Dependence of Growth Mode of HFCVD Diamond, 81
  - Optical properties and microstructure of CVD diamond films, 153
  - LWIR spectral properties of CVD diamond at cryogenic temperatures, 169
  - Insulating diamond coatings on tungsten electrodes, 293
  - The characterization of single structure diamond heater and temperature sensor, 394
  - Mass spectrometry and diamond growth from CCl<sub>4</sub>/H<sub>2</sub> gas mixtures, 490
  - Evaluation of MPCVD diamond film adhesion on hard metal substrates by micro Raman spectroscopy, 769
  - Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807
  - Nanoscale grinding of ceramics using diamond fibres, 893
  - Formation mechanisms of diamond precursors during the nucleation process, 1047
  - Atomic hydrogen-induced chemical vapor deposition of a-Si:C:H thin-film materials from alkylsilane precursors, 1081
  - Photoconductivity of CVD diamond under bandgap and subbandgap irradiations, 1157
  - Morphologies of diamond films from atomic-scale simulations of chemical vapor deposition, 1198
  - Optical monitoring of the growth of 3C SiC on Si in a CVD reactor, 1857
- CVD-diamond**
- Raman and photoluminescence microscopy mapping of CVD micro-diamonds, 1587
- CVD diamond**
- Design-to-implementation case studies of CVD diamond in r.f./microwave package and detector applications, 191
  - A micro-IBIC comparison between natural and CVD diamond, 320
  - Neutron damage of CVD diamond, 353
- Deposition of CVD diamond onto boron carbide substrates, 450
  - TEM investigations on the heteroepitaxial nucleation of CVD diamond on (001) silicon substrates, 752
  - Wide frequency dielectric properties of CVD diamond, 856
  - Field-emission studies of boron-doped CVD diamond films following surface treatments, 1135
  - The activation energy for diamond growth from CCl<sub>4</sub>/H<sub>2</sub> mixtures in a hot-filament reactor, 1172
  - Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226
  - Low frequency noise in silicon carbide Schottky diodes, 1494
  - Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
  - Emission and excitation spectra of silicon-related luminescent centers in CVD-grown diamond films, 1564
  - Diamond seed incorporation by electrochemical treatment of silicon substrate, 1629
- CVD diamond films**
- Quantitative study of Raman scattering and defect optical absorption in CVD diamond films, 704
  - The optical characterization of boron-doped MPCVD diamond films, 940
  - Diamond film deposition by a substrate-stabilized flat flame, 1599
- CVD diamond growth**
- Examination of the effects of nitrogen on the CVD diamond growth mechanism using in situ molecular beam mass spectrometry, 247
- CVD diamond parts**
- Cylindrically symmetric diamond parts by hot-filament CVD, 1707
- CVD microwave**
- Heteroepitaxial diamond growth process on platinum (111), 266
- Cyclic voltammetry**
- Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17
- Cyclotron resonance**
- Contactless characterisation of 2D-electrons in GaN/AlGaN HFETs, 1536
- 2-D numerical analysis**
- Numerical study of avalanche breakdown of 6H-SiC planar *p-n* junctions, 1500
- D.c./r.f. plasma**
- Preparation of crystalline carbon nitride films on silicon substrate by chemical vapor deposition, 635
- DC plasma CVD**
- Diamond growth on a large area and some aspects of diamond nucleation, 426
  - Thermal gas effusion from diamond-like carbon films, 1830
- D.C. Plasma jet**
- Deposition of diamond from plasma jets with chlorobenzenes as carbon source, 1874
- D.C. polarization**
- Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17
- Decay time**
- Measurement of decay time for the NV centre in Ib diamond with a picosecond laser pulse, 1595
- Deep levels**
- Deep luminescent centres in electron-irradiated 6H SiC, 1378
  - Characterization of electrically active deep level defects in 4H and 6H SiC, 1388
- Deep level transient spectroscopy**
- Radiation-induced defect centers in 4H silicon carbide, 1333

- Defect**
- Paramagnetic centres in tetrahedral amorphous carbon, 783
  - Investigation of lattice impurities and photochromic centres in diamond with high resolution positron annihilation spectroscopy, 1777
- Defect centers**
- Emission and excitation spectra of silicon-related luminescent centers in CVD-grown diamond films, 1564
- Defects**
- High temperature Young's modulus of polycrystalline diamond, 344
  - The influence of boron doping on the structure and characteristics of diamond thin films, 521
  - Cathodoluminescence spectroscopy of synthetic diamond films, 717
  - Minimization of the defects concentration from boron incorporation in polycrystalline diamond films, 778
  - Measurement and calculation of the thermal expansion coefficient of diamond, 839
  - Defects formation in sublimation grown 6H-SiC single crystal boules, 1249
  - Deep luminescent centres in electron-irradiated 6H SiC, 1378
  - Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers, 1381
  - Preferential etching of SiC crystals, 1456
- Defeits**
- Characterization of electrically active deep level defects in 4H and 6H SiC, 1388
- Delamination**
- Deposition of CVD diamond onto boron carbide substrates, 450
- Density of interface states**
- "Carbon cluster model" for electronic states at SiC/SiO<sub>2</sub> interfaces, 1472
- Density of states**
- Electrical properties of PECVD amorphous silicon–carbon alloys from amorphous–crystalline heterojunctions, 1555
- Depocilion**
- A multilayer approach to high adhesion diamond-like carbon coatings on titanium, 802
- Deposition**
- Diamond film deposition by a substrate-stabilized flat flame, 1599
  - Capabilities of combined studies of DLC films by X-ray methods, 1784
- Detectors**
- Design-to-implementation case studies of CVD diamond in r.f./microwave package and detector applications, 191
- Device**
- High temperature polycrystalline diamond metal-insulator-semiconductor field-effect-transistor, 333
  - Enhancement/depletion MESFETs of diamond and their logic circuits, 339
  - The characterization of single structure diamond heater and temperature sensor, 394
  - Device modeling of high performance diamond MESFETs using p-type surface semiconductive layers, 865
- Device modeling**
- The potential of SiC and GaN for application in high speed devices, 1512
- Diamond**
- Pressure Dependence of Growth Mode of HFCVD Diamond, 81
  - Electron beam-induced current imaging of chemical vapor-deposited diamond films, 95
  - Effect of nitrogen concentration on plasma reactivity and diamond growth in a H<sub>2</sub>–CH<sub>4</sub>–N<sub>2</sub> microwave discharge, 107
  - Stresses generated by inhomogeneous distributions of inclusions in diamonds, 120
- Optical properties and microstructure of CVD diamond films, 153**
- LWIR spectral properties of CVD diamond at cryogenic temperatures, 169**
- Low pressure polymer precursor process for synthesis of hard glassy carbon and diamond films, 230**
- Insulating diamond coatings on tungsten electrodes, 293**
- High temperature polycrystalline diamond metal-insulator-semiconductor field-effect-transistor, 333**
- Photoconductive properties of thin film diamond, 374**
- Characterization of metal–diamond interfaces: electron affinity and Schottky barrier height, 398**
- Characterization of the microstructure of diamond pyramidal microtip emitters, 403**
- Diamond growth on a large area and some aspects of diamond nucleation, 426**
- Effects of electron and atomic hydrogen irradiation on gas-source molecular beam epitaxy of diamond with pure methane, 463**
- H actinometry with CF<sub>4</sub> addition in microwave plasma-assisted chemical vapor deposition of diamond, 472**
- Combined effect of nitrogen and pulsed microwave plasma on diamond growth, 505**
- Growth of diamond films from a continuous or interrupted CF<sub>4</sub> supply, 511**
- The chemical nature of the carbon precursor in bias-enhanced nucleation of CVD diamond, 526**
- Microstructure and growth of MWCVD diamond on Si<sub>1-x</sub>C<sub>x</sub> buffer layers, 649**
- Biased enhanced nucleation of diamond on metals: an OES and electrical investigation, 658**
- Kinetics of the initial stages of CVD diamond growth on non-diamond substrates: surface catalytic effects and homoepitaxy, 681**
- Thermal-programmed desorption (TPD) of deuterium from Di(111) surface: presence of two adsorption states, 736**
- Mechanism of surface smoothing of diamond by a hydrogen plasma, 791**
- Adhesion improvement of diamond films on steel substrates using chromium nitride interlayers, 796**
- Elastic properties of polycrystalline cubic boron nitride and diamond by dynamic resonance measurements, 812**
- The effect of varying deposition conditions on the Young's modulus of diamond coated wires, 817**
- Factors affecting the fracture strength and Young's modulus of CVD diamond-coated fibres, 826**
- Carrier transport mechanisms through the metal/p-type diamond semiconductor interface, 847**
- Enhancing low field electron emission from polycrystalline diamond, 869**
- Nanoscale grinding of ceramics using diamond fibres, 893**
- Diamond fibre metal matrix composites, 898**
- Optical properties of diamond film deposited by CVD of Freon: studies on mechanical properties from the absorption band tail, 991**
- Growth and defects of diamond facets under negative biasing conditions in a microwave plasma CVD process, 1010**
- Formation mechanisms of diamond precursors during the nucleation process, 1047**
- Transient nucleation of diamond: theoretical and experimental study, 1092**
- On the {111} penetration twin density in CVD diamond films, 1697**
- Nucleation enhancement behavior of diamond on Si substrate according to surface treatment materials, 1716**
- Sequential multiple-laser-assisted polishing of free-standing CVD diamond substrates, 1789**
- Diamond membranes with controlled porosity, 1824**

- Diamond-like carbon**
- Microtribological properties of diamond-like and hydrogenated carbon coatings grown by different methods, 1
  - Electronic structure of diamond-like carbon, 212
  - Evaluation of diamond-like carbon-coated orthopaedic implants, 390
  - Characterization and optimization of mid-frequency plasma-enhanced chemical vapour deposited carbon films using response surface methodology, 537
  - Studies of nanoscale structure and its transformation in pulsed-laser deposited dense diamond-like carbon films, 564
  - A multilayer approach to high adhesion diamond-like carbon coatings on titanium, 802
  - Experimental and theoretical studies of growth mechanisms of hard wear-resistant carbon-based films on three-dimensional substrates, 970
  - The drift mobility and decay of photocurrent in doped amorphous diamond-like carbon films, 1152
  - Thermal gas effusion from diamond-like carbon films, 1830
  - Influence of nitrogen doping on photoconductivity properties of a: DLC films, 1868
- Diamond-like carbon (DLC)**
- Optical and photoemission studies of DLC films prepared with a systematic variation of the  $sp^3:sp^2$  composition, 687
- Diamond-like films**
- Production and characterisation of amorphic diamond films produced by pulsed laser ablation of graphite, 569
  - Diamond-like hydrogenated amorphous carbon films studied by X-ray emission spectroscopy, 944
  - DLC growth by ion beam assisted deposition: a molecular simulation, 1638
- Diamond coatings**
- On the mechanical integrity ratio of diamond coatings, 348
- Diamond crystal growth**
- Deposition of diamond from plasma jets with chlorobenzenes as carbon source, 1874
- Diamond CVD**
- Formation of nanocrystalline diamond by hydrocarbon plasma beam deposition, 255
- Diamond defects**
- Phosphorescence in high-pressure synthetic diamond, 99
  - Initial results of a novel pre-deposition seeding technique for achieving an ultra-high nucleation density for CVD diamond growth, 430
  - Gap density of states in CVD diamond films from photoconductivity and photoluminescence data, 712
  - Photoconductivity of CVD diamond under bandgap and subbandgap irradiations, 1157
  - Charge carrier trapping centers in synthetic diamond, 1674
- Diamond deposition**
- Diamond deposition in a microwave electrode discharge at reduced pressures, 224
  - Features of diamond deposition on modified silica glass substrates, 444
  - Diamond deposition and plasma diagnostics in a 27 MHz inductive coupled reactor (ICP), 1816
- Diamond fibre**
- Diamond fibres by a hot filament CVD process, 822
- Diamond film**
- Large-area diamond deposition by microwave plasma, 417
  - Total-dose hardness integrated circuit fabricated with silicon-on-diamond structured wafer, 673
  - Effect of boron incorporation on the structure of polycrystalline diamond films, 774
  - Minimization of the defects concentration from boron incorporation in polycrystalline diamond films, 778
- Excimer laser-induced electron emission from diamond films, 1650
- A study of the initial stages of diamond deposition on ferrous substrates coated by a nitrided chromium interlayer and on nitrided polycrystalline chromium substrates, 1847
- Diamond film growth**
- Effects of simultaneous boron and nitrogen addition on hot-filament CVD diamond growth, 456
  - Investigation of the boron incorporation in polycrystalline CVD diamond films by TEM, EELS and Raman spectroscopy, 763
- Diamond films**
- Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17
  - Nanocrystalline diamond films: transmission electron microscopy and Raman spectroscopy characterization, 159
  - Thermal resistance and electrical insulation of thin low-temperature-deposited diamond films, 298
  - High-voltage Schottky diode on epitaxial diamond layer, 329
  - Diamond coatings for IR window applications, 386
  - The characterization of single structure diamond heater and temperature sensor, 394
  - Free-standing diamond film preparation using copper substrate, 422
  - On the development of CVD diamond film morphology due to the twinning on {111} surfaces, 435
  - Energy distribution of H atom and C<sub>2</sub> radical during diamond growth in H<sub>2</sub>/Ar-CH<sub>4</sub>-O<sub>2</sub> plasma, 468
  - Effect of surface species concentrations and temperature on diamond film morphology in inductively coupled r.f. plasma CVD, 481
  - The influence of boron doping on the structure and characteristics of diamond thin films, 521
  - Nucleation and initial growth of bias-assisted HFCVD diamond on boron nitride films, 579
  - Interfacial analysis of CVD diamond on copper substrates, 743
  - Evaluation of MPCVD diamond film adhesion on hard metal substrates by micro Raman spectroscopy, 769
  - Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807
  - Electron emission characteristics of metal/diamond field emitters, 889
  - Effect of substrate on the characteristics of the interface between diamond film and substrate, 959
  - Calculation of the stress in large square facets of MPCVD grown diamond from cathodoluminescence and raman spectroscopy measurements and comparison to stress predicted from finite element models, 1062
  - An experimental study of high pressure synthesis of diamond films using a microwave cavity plasma reactor, 1097
  - In-situ ellipsometry study of initial stage of bias-enhanced nucleation and heteroepitaxy of diamond on silicon(100) by hot filament chemical vapor deposition, 1117
  - Morphologies of diamond films from atomic-scale simulations of chemical vapor deposition, 1198
  - The crystallographic relationship of heteroepitaxial diamond films on scratched silicon substrates, 1836
- Diamond growth**
- Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17
  - Diamond growth in a direct-current low-pressure supersonic plasmajet, 406
  - Mass spectrometry and diamond growth from CCl<sub>4</sub>/H<sub>2</sub> gas mixtures, 490
  - Diamond growth in and above trenches in silicon, 1019
  - Growth and characterisation of CVD diamond wires for X-ray detection, 1051

- Simulation of morphological instabilities during diamond chemical vapor deposition, 1759
- Diamond microcrystals**  
Small scale electronic transport in diamond microcrystals, 325
- Diamond nucleation**  
Mechanisms of CVD diamond nucleation and growth on mechanically scratched and virgin Si(100) surfaces, 235  
Diamond deposition on noble metals, 240  
Diamond nucleation enhancement by hydrofluoric acid etching of silicon substrate, 440  
Optimising control of microwave plasma bias enhanced nucleation for heteroepitaxial chemical vapour deposition diamond, 676  
Diamond nucleation on silicon during bias treatment in chemical vapour deposition as analysed by electron microscopy, 747  
The effect of ultrasonic vibration on CVD diamond nucleation, 1031
- Diamond nucleation and growth**  
Optimization of MW-PACVD diamond deposition parameters for high nucleation density and growth rate on  $\text{Si}_3\text{N}_4$  substrate, 411
- Diamond nuclei**  
Improvement of diamond nuclei orientation by double-step bias treatment in microwave plasma-assisted chemical vapor deposition using  $\text{C}_2\text{H}_4$  and  $\text{CH}_4$  as carbon source, 668
- Diamond polishing**  
Friction tracks on diamond surfaces imaged by atomic force microscopy, 975
- Diamond powder**  
Comparative study of optical absorption in diamond powders and polycrystalline CVD films, 1124
- Diamonds**  
The measurement of thermal properties of diamond, 1057  
The aggregation of nitrogen and the formation of A centres in diamonds, 1643
- Diamond thin films**  
Heteroepitaxial growth of diamond thin films on silicon: information transfer by epitaxial tilting, 935
- Dielectric properties**  
Wide frequency dielectric properties of CVD diamond, 856
- Diffusion**  
Spatially resolved measurements of absolute  $\text{CH}_3$  concentration in a hot-filament reactor, 476  
Structure and properties of a-C:H films deposited onto polymeric substrates, 551  
Formation peculiarities of the interfacial structure during cBN wetting with Ag-Ti, Ag-Zr and Ag-Hf alloys, 931  
A study of the initial stages of diamond deposition on ferrous substrates coated by a nitrided chromium interlayer and on nitrided polycrystalline chromium substrates, 1847
- Diffusion (surface)**  
Mechanism of surface smoothing of diamond by a hydrogen plasma, 791
- Diodes**  
2.5 kV ion-implanted  $p^+n$  diodes in 6H-SiC, 1485
- Direct-current low-pressure supersonic plasmajet**  
Diamond growth in a direct-current low-pressure supersonic plasmajet, 406
- Dissolution**  
Growth of SiC from the liquid phase: wetting and dissolution of SiC, 1266
- DLC**  
Effect of negative bias voltage on a-C:H films deposited in electron cyclotron resonance plasma, 542  
Diamond-like carbon metal-semiconductor-metal switches for active matrix displays, 879  
Capabilities of combined studies of DLC films by X-ray methods, 1784
- DLC films**  
Use of diamond-like carbon films in X-ray optics, 902  
Deposition of DLC films in  $\text{CH}_4/\text{Ne}$  and  $\text{CH}_4/\text{Kr}$  r.f. plasmas, 547
- DLTS**  
Characterization of electrically active deep level defects in 4H and 6H SiC, 1388
- Doping**  
Nitrogen doping of diamond by ion implantation, 516  
Nitrogen and iodine doping in amorphous diamond-like carbon films, 555  
Electronic and atomic structure of undoped and doped ta-C films, 830  
The drift mobility and decay of photocurrent in doped amorphous diamond-like carbon films, 1152  
Influence of nitrogen doping on photoconductivity properties of a: DLC films, 1868
- Doping of impurity**  
Electrical properties of B-doped homoepitaxial diamond (001) film, 1753
- Double-step bias treatment**  
Improvement of diamond nuclei orientation by double-step bias treatment in microwave plasma-assisted chemical vapor deposition using  $\text{C}_2\text{H}_4$  and  $\text{CH}_4$  as carbon source, 668
- Drift**  
Investigation of walk-out phenomena in SiC mesa diodes with  $\text{SiO}_2/\text{Si}_3\text{N}_4$  passivation, 1476
- DTA**  
Investigation of the c-BN/h-BN phase transformation at normal pressure, 286
- Dynamical reflectivity**  
Optical monitoring of the growth of 3C SiC on Si in a CVD reactor, 1857
- ECR-CVD**  
Microwave power effects on the properties of phosphorus-doped SiC:H films prepared using ECR-CVD, 48
- ECR plasma**  
Effect of negative bias voltage on a-C:H films deposited in electron cyclotron resonance plasma, 542
- EELS**  
Effect of negative bias voltage on a-C:H films deposited in electron cyclotron resonance plasma, 542  
Investigation of the boron incorporation in polycrystalline CVD diamond films by TEM, EELS and Raman spectroscopy, 763
- Effective masses**  
Progress in the study of optical and related properties of SiC since 1992, 1243
- Effective Richardson coefficient**  
Structural and electrical properties of Schottky barriers on n-GaN, 1528
- Elastic recoil detection**  
Preparation of  $\text{CN}_x$  films by ion beam assisted filtered cathodic arc deposition, 626
- Electrical**  
Nitrogen and iodine doping in amorphous diamond-like carbon films, 555
- Electrical activation**  
Investigation of the effects of high temperature implantation and post implantation annealing on the electrical behavior of nitrogen implanted  $\beta$ -SiC films, 1445
- Electrical conductivity**  
Paramagnetic centres in tetrahedral amorphous carbon, 783

- Optical and electrical characteristics of amorphous diamond films**, 983
- Electrical insulation**
- Thermal resistance and electrical insulation of thin low-temperature-deposited diamond films, 298
- Electrical noise**
- Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226
  - Low frequency noise in silicon carbide Schottky diodes, 1494
  - Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- Electrical properties**
- Insulating diamond coatings on tungsten electrodes, 293
  - A micro-IBIC comparison between natural and CVD diamond, 320
  - High temperature polycrystalline diamond metal-insulator-semiconductor field-effect-transistor, 333
  - Photoelectrical characteristics of diamond UV detectors: dependence on device design and film quality, 361
  - Production and characterisation of amorphic diamond films produced by pulsed laser ablation of graphite, 569
  - Carrier transport mechanisms through the metal/p-type diamond semiconductor interface, 847
  - Capacitance–voltage measurements on metal– $\text{SiO}_2$ –boron-doped homoepitaxial diamond, 852
  - Wide frequency dielectric properties of CVD diamond, 856
  - Electrical conduction in polycrystalline diamond and the effects of UV irradiation, 860
  - Enhancing low field electron emission from polycrystalline diamond, 869
  - Diamond-like carbon metal–semiconductor–metal switches for active matrix displays, 879
  - Growth and characterisation of CVD diamond wires for X-ray detection, 1051
  - Electrical properties and thermal stability of ion beam deposited BN thin films, 1129
  - Charge carrier trapping centers in synthetic diamond, 1674
  - An impedance spectroscopy investigation of polycrystalline diamond from dc to 1 GHz, 1689
  - Electrical properties of B-doped homoepitaxial diamond (001) film, 1753
- Electron**
- Effects of electron and atomic hydrogen irradiation on gas-source molecular beam epitaxy of diamond with pure methane, 463
- Electron affinity**
- Characterization of metal–diamond interfaces: electron affinity and Schottky barrier height, 398
  - Characterization of the microstructure of diamond pyramidal microtip emitters, 403
- Electron beam brazing**
- Investigation of contact phenomena at cubic boron nitride–filler metal interface during electron beam brazing, 1067
- Electron beam lithography;**
- Small scale electronic transport in diamond microcrystals, 325
- Electron cyclotron resonance**
- Influence of substrate temperature and microwave power on the properties of a-C:H films prepared using the ECR-CVD method, 1683
- Electron emission**
- Production and characterisation of amorphic diamond films produced by pulsed laser ablation of graphite, 569
  - Electron emission characteristics of metal/diamond field emitters, 889
- Electron field emission**
- Electron field emission from thin fine-grained CVD diamond films, 1111
- Electronic band structure**
- Valence band dispersion of hexagonal SiC, 1342
- Electronic field**
- High field/high temperature performance of semi-insulating silicon carbide, 1392
- Electronic packaging**
- Design-to-implementation case studies of CVD diamond in r.f./microwave package and detector applications, 191
- Electronic states**
- Angle resolved photoemission and the band structure of 6H-SiC, 1358
- Electronic structure**
- Electronic structure of diamond-like carbon, 212
- Electron irradiation**
- Deep luminescent centres in electron-irradiated 6H SiC, 1378
- Electron microscopy**
- Nanocrystalline diamond films: transmission electron microscopy and Raman spectroscopy characterization, 159
  - Diamond nucleation on silicon during bias treatment in chemical vapour deposition as analysed by electron microscopy, 747
  - Micropipe defects and voids at  $\beta$ -SiC/Si(100) interfaces, 1365
  - TEM study of Ni and  $\text{Ni}_2\text{Si}$  ohmic contacts to SiC, 1428
  - The crystallographic relationship of heteroepitaxial diamond films on scratched silicon substrates, 1836
- Electron spectroscopies**
- Mechanisms of CVD diamond nucleation and growth on mechanically scratched and virgin Si(100) surfaces, 235
  - AES and XPS observations of HFCVD diamond deposition on monocrystalline (111) copper, 664
- Electron spectroscopy**
- The roles of H and O atoms in diamond growth, 486
  - Paramagnetic centres in tetrahedral amorphous carbon, 783
  - Electronic and atomic structure of undoped and doped ta-C films, 830
  - Tuning the electron affinity of CVD diamond with adsorbed caesium and oxygen layers, 874
- Electron spin resonance**
- Insight on the microscopical structure of a-C and a-C:H thin films through electron spin resonance analysis, 725
- Ellipsometry**
- In-situ ellipsometry study of initial stage of bias-enhanced nucleation and heteroepitaxy of diamond on silicon(100) by hot filament chemical vapor deposition, 1117
  - Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226
  - Low frequency noise in silicon carbide Schottky diodes, 1494
  - Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- Emission**
- Characterization of metal–diamond interfaces: electron affinity and Schottky barrier height, 398
  - Characterization of the microstructure of diamond pyramidal microtip emitters, 403
- Emission sites**
- Electron field emission from thin fine-grained CVD diamond films, 1111
- Emission time**
- Hysteresis loop in the current–voltage characteristic of Al/boron-doped polycrystalline diamond Schottky contact, 12
- Encapsulation**
- A two-step process for the formation of a  $\text{Mo}_2\text{C}$  contact on polycrystalline diamond films, 843
- Energy mass spectrometry**
- Diamond deposition and plasma diagnostics in a 27 MHz inductive coupled reactor (ICP), 1816

- Epitaxial  $\beta$ -SiC**  
Topology of twin junctions in epitaxial  $\beta$ -SiC, 1362
- Epitaxial layer uniformity**  
Optical investigation of thick 3C-SiC layers deposited on bulk silicon by CVD, 1385
- Epitaxial SiC films**  
Infra-red characterization of carbonization of Si surfaces by gas source molecular beam epitaxy, 1772
- Epitaxial tilting**  
Heteroepitaxial growth of diamond thin films on silicon: information transfer by epitaxial tilting, 935
- Epitaxy**  
The origin of 3C polytype inclusions in epitaxial layers of silicon carbide grown by chemical vapour deposition, 1297
- EPR**  
Nitrogen doping of diamond by ion implantation, 516
- Etching**  
Diamond deposition from halogenated methane precursors on Si and SiC substrates, 85
- Etching of graphite and diamond by thermal energy hydrogen atoms, 787
- Reactive ion etching of diamond as a means of enhancing chemically-assisted mechanical polishing efficiency, 952
- Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226
- Preferential etching of SiC crystals, 1456
- Low frequency noise in silicon carbide Schottky diodes, 1494
- Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- Evaporation**  
Formation of cubic boron nitride thin films by reactive cathodic arc evaporation, 1005
- Excimer laser irradiation**  
Excimer laser-induced electron emission from diamond films, 1650
- Experiments**  
Progress in the study of optical and related properties of SiC since 1992, 1243
- Extended crystalline defects**  
Sublimation growth of 4H- and 6H-SiC boule crystals, 1262
- $\beta$ -factor**  
Thermodynamic properties of  $^{13}\text{C}$ -diamond, 172
- Fibres**  
The effect of varying deposition conditions on the Young's modulus of diamond coated wires, 817
- Factors affecting the fracture strength and Young's modulus of CVD diamond-coated fibres, 826
- Nanoscale grinding of ceramics using diamond fibres, 893
- Diamond fibre metal matrix composites, 898
- Field-emission**  
Field-emission studies of boron-doped CVD diamond films following surface treatments, 1135
- Field electron emission**  
Excimer laser-induced electron emission from diamond films, 1650
- Field emitter**  
Electron emission characteristics of metal/diamond field emitters, 889
- Filler metal**  
Investigation of contact phenomena at cubic boron nitride-filler metal interface during electron beam brazing, 1067
- Filtered cathodic vacuum arc**  
Boronated tetrahedral amorphous carbon (ta-C:B), 207
- First principles calculation**  
Polytypism and surface structure of SiC, 1346
- Floating ring**  
Numerical study of avalanche breakdown of 6H-SiC planar  $p-n$  junctions, 1500
- Fluorine**  
Investigations concerning the role of fluorine and chlorine in the low temperature growth of diamond, 964
- Fourier-transform infrared spectroscopy**  
Raman spectroscopy investigation of cubic boron nitride single crystals and layers on Si(100), 612
- Fowler-Nordheim injection**  
High field and high temperature stress of n-SiC MOS capacitors, 1489
- Free-standing**  
Free-standing diamond film preparation using copper substrate, 422
- Measurement and calculation of the thermal expansion coefficient of diamond, 839
- Free exciton recombination radiation**  
Comparative study of excitonic recombination radiation from diamonds grown by CVD and HP/HT methods, 1668
- Friction coefficient**  
[100]-Textured diamond films for tribological applications, 381
- Friction tracks**  
Friction tracks on diamond surfaces imaged by atomic force microscopy, 975
- FTIR**  
The optical characterization of boron-doped MPCVD diamond films, 940
- Growth of AlN thin films on (111) and (100) silicon by pulsed laser deposition in nitrogen plasma ambient, 1015
- FTIR-spectroscopy**  
C-BN thin film formation in a hybrid r.f.-PLD technique, 599
- Funnels**  
Cylindrically symmetric diamond parts by hot-filament CVD, 1707
- GaAs<sub>1-x</sub>N<sub>x</sub> thin films**  
Amorphous GaAs<sub>1-x</sub>N<sub>x</sub> thin films on crystalline Si substrates: growth and characterizations, 1568
- Gallium nitride**  
Residual strains in GaN grown on 6H-SiC, 1524
- Gallium nitrides**  
Structural properties of GaN grown on SiC substrates by hydride vapor phase epitaxy, 1532
- GaN**  
Growth, doping and characterization of Al<sub>x</sub>Ga<sub>1-x</sub>N thin film alloys on 6H-SiC(0001) substrates, 196
- Structural and electrical properties of Schottky barriers on n-GaN, 1528
- Identification of the cubic and hexagonal polytypes of GaN with X-ray absorption measurements, 1539
- GaN/GaAlN heterostructures**  
Contactless characterisation of 2D-electrons in GaN/AlGaN HFETs, 1536
- Gap states**  
Hydrogen-related gap states in the near surface of chemical vapor deposited homoepitaxial diamond films, 303
- Gas-MBE growth**  
Infra-red characterization of carbonization of Si surfaces by gas source molecular beam epitaxy, 1772
- Gas-phase species**  
Examination of the effects of nitrogen on the CVD diamond growth mechanism using in situ molecular beam mass spectrometry, 247

- Gas mixtures**  
 Mass spectrometry and diamond growth from  $\text{CCl}_4/\text{H}_2$  gas mixtures, 490
- Gas phase**  
 Cubic boron nitride synthesis by pyrolysis of certain polyammoniates of boron hydrides of metals at high pressure, 987
- Gate oxide**  
 Passivation of interface traps in MOS-Devices on *n*- and *p*-type 6H-SiC, 1497
- Gauge factor**  
 Piezoresistive property of CVD diamond films, 367
- GH-SiC, p-n junction**  
 Numerical study of avalanche breakdown of 6H-SiC planar *p-n* junctions, 1500
- Glassy carbon**  
 Low pressure polymer precursor process for synthesis of hard glassy carbon and diamond films, 230
- Glow discharge**  
 Effects of thermal and laser annealing on silicon carbide nanopowder produced in radio frequency glow discharge, 1559
- Graphite**  
 Transmission electron microscope study of heteroepitaxial diamond on Pt (111), 272  
 Effects of simultaneous boron and nitrogen addition on hot-filament CVD diamond growth, 456  
 Raman and photoluminescence microscopy mapping of CVD micro-diamonds, 1587
- Graphite/diamond**  
 Etching of graphite and diamond by thermal energy hydrogen atoms, 787
- Graphitic carbon**  
 How plastic deformation can produce texture in graphitic films of boron nitride, carbon nitride, and carbon, 1219
- Growth**  
 Enhanced deposition rate of diamond in atmospheric pressure plasma CVD: effects of a secondary discharge, 202  
 Characterization and growth of carbon phases synthesized by high temperature carbon ion implantation into copper, 261  
 Large-area diamond deposition by microwave plasma, 417  
 On the development of CVD diamond film morphology due to the twinning on {111} surfaces, 435  
 Growth of diamond films from a continuous or interrupted  $\text{CF}_4$  supply, 511  
 Nucleation and initial growth of bias-assisted HFCVD diamond on boron nitride films, 579  
 Growth and characterisation of boron nitride films: layer sequence and phase identification, 594  
 Growth and defects of diamond facets under negative biasing conditions in a microwave plasma CVD process, 1010  
 Growth of SiC from the liquid phase: wetting and dissolution of SiC, 1266
- Growth conditions**  
 Electron field emission from thin fine-grained CVD diamond films, 1111
- Growth mechanisms models**  
 Experimental and theoretical studies of growth mechanisms of hard wear-resistant carbon-based films on three-dimensional substrates, 970
- Growth model**  
 The kinetic growth model applied to micropipes in 6H-SiC, 1269
- Growth states**  
 Growth stages of chemical vapor deposited diamond on the titanium alloy Ti-6Al-4V, 1658
- 4H SiC**  
 Growth-related structural defects in seeded sublimation-grown SiC, 1272
- 4H silicon carbide**  
 Radiation-induced defect centers in 4H silicon carbide, 1333
- 6H-, 4H-SiC**  
 Hydrogen incorporation in epitaxial layers of 4H- and 6H-silicon carbide grown by vapor phase epitaxy, 1293
- 6H SiC**  
 Growth-related structural defects in seeded sublimation-grown SiC, 1272
- H-BN**  
 Investigation of the c-BN/h-BN phase transformation at normal pressure, 286
- 4H-SiC**  
 High quality 4H-SiC grown on various substrate orientations, 1289
- 6H-SiC**  
 Angle resolved photoemission and the band structure of 6H-SiC, 1358  
 OBIC studies on 6H-SiC Schottky rectifiers with different surface pretreatments, 1396  
 Temperature dependence of electrical properties of 6H-SiC buried gate JFET, 1504
- Hafnium**  
 Hafnium, cadmium and indium impurities in 4H-SiC observed by perturbed angular correlation spectroscopy, 1436
- Halide chemistry**  
 Growth of diamond films from a continuous or interrupted  $\text{CF}_4$  supply, 511  
 The activation energy for diamond growth from  $\text{CCl}_4/\text{H}_2$  mixtures in a hot-filament reactor, 1172
- Halogenated**  
 Diamond deposition from halogenated methane precursors on Si and SiC substrates, 85
- Halomethane**  
 Diamond deposition from halogenated methane precursors on Si and SiC substrates, 85
- Hardness**  
 Mechanical properties of synthetic type IIa diamond crystal, 1841
- Heat diffusion**  
 Thermal properties of  $\beta$ -SiC epitaxial layers between 150 C and 500 C measured by using microstructures, 1338
- Heated filament**  
 Growth of diamond films from a continuous or interrupted  $\text{CF}_4$  supply, 511
- Heteroepitaxial growth**  
 Heteroepitaxial growth of diamond thin films on silicon: information transfer by epitaxial tilting, 935
- Heteroepitaxial nucleation**  
 TEM investigations on the heteroepitaxial nucleation of CVD diamond on (001) silicon substrates, 752
- Heteroepitaxy**  
 Heteroepitaxial diamond growth process on platinum (111), 266  
 Transmission electron microscope study of heteroepitaxial diamond on Pt (111), 272  
 Surface characterization of smooth heteroepitaxial diamond layers on  $\beta$ -SiC (001), 277  
 Modeling interface structures of cubic boron nitride films deposited heteroepitaxially and via a hexagonal boron nitride interlayer on silicon (001) surfaces, 589  
 Microstructure and growth of MWCVD diamond on  $\text{Si}_{1-x}\text{C}_x$  buffer layers, 649  
 Optimising control of microwave plasma bias enhanced nucleation for heteroepitaxial chemical vapour deposition diamond, 676

- The crystallographic relationship of heteroepitaxial diamond films on scratched silicon substrates, 1836
- Heteroepitaxy/homoepitaxy**
- Growth and defects of diamond facets under negative biasing conditions in a microwave plasma CVD process, 1010
- Heterogeneous nucleation**
- Transient nucleation of diamond: theoretical and experimental study, 1092
- Heterojunction**
- Electrical properties of PECVD amorphous silicon–carbon alloys from amorphous–crystalline heterojunctions, 1555
- Hexagonal polytypes**
- Identification of the cubic and hexagonal polytypes of GaN with X-ray absorption measurements, 1539
- HFCVD**
- Diamond fibres by a hot filament CVD process, 822
  - Growth and characterisation of CVD diamond wires for X-ray detection, 1051
- High frequency**
- An impedance spectroscopy investigation of polycrystalline diamond from dc to 1 GHz, 1689
- High pressure**
- X-ray diffraction analysis of aluminum nitride sintered with cubic boron nitride, 927
  - Cubic boron nitride synthesis by pyrolysis of certain polyammoniates of boron hydrides of metals at high pressure, 987
- High pressure/high temperature**
- Phosphorescence in high-pressure synthetic diamond, 99
  - ESR studies of incorporation of phosphorus into high-pressure synthetic diamond, 356
  - Distribution of the cobalt-related luminescence center in HPHT diamond, 708
- High pressure and high temperature method**
- Comparative study of excitonic recombination radiation from diamonds grown by CVD and HP/HT methods, 1668
- High pressure crystal growth**
- Mechanical properties of synthetic type IIa diamond crystal, 1841
- High quality diamond films**
- High quality diamond films on WC–Co surfaces, 89
- High resistivity**
- Amorphous  $\text{GaAs}_{1-x}\text{N}_x$  thin films on crystalline Si substrates: growth and characterizations, 1568
- High resonance frequencies**
- Fabrication of integrated diamond cantilevers with tips for SPM applications, 906
- High speed devices**
- The potential of SiC and GaN for application in high speed devices, 1512
- High temperature**
- X-ray diffraction analysis of aluminum nitride sintered with cubic boron nitride, 927
  - Thermal properties of  $\beta$ -SiC epitaxial layers between 150 °C and 500 °C measured by using microstructures, 1338
  - $\beta$ -SiC films on SOI substrates for high temperature applications, 1448
- High temperature annealing**
- The 0.545 eV center in neutron irradiated and annealed type Ib diamond, 1722
- High temperature nitrogen implantation**
- Investigation of the effects of high temperature implantation and post implantation annealing on the electrical behavior of nitrogen implanted  $\beta$ -SiC films, 1445
- Hillock growth**
- A study on surface morphologies of (001) homoepitaxial diamond films, 130
- Hollow fibres**
- Diamond fibre metal matrix composites, 898
- Homoepitaxial (001) diamond films**
- A study on surface morphologies of (001) homoepitaxial diamond films, 130
- Homoepitaxial diamond**
- Electrical properties of B-doped homoepitaxial diamond (001) film, 1753
- Homoepitaxial diamond films**
- Liftoff-technique of single-crystal diamond plates: study of the lattice damage of the implanted substrates and the crystalline quality of the homoepitaxial films by ion channelling, 149
  - Hydrogen-related gap states in the near surface of chemical vapor deposited homoepitaxial diamond films, 303
- Homoepitaxy**
- Lift-off technique of homoepitaxial CVD diamond films by deep implantation and selective etching, 654
  - Kinetics of the initial stages of CVD diamond growth on non-diamond substrates: surface catalytic effects and homoepitaxy, 681
  - Capacitance–voltage measurements on metal– $\text{SiO}_2$ –boron-doped homoepitaxial diamond, 852
  - The optical characterization of boron-doped MPCVD diamond films, 940
- Hot filament**
- Cylindrically symmetric diamond parts by hot-filament CVD, 1707
- Hot filament assisted CVD**
- Deposition of carbon nitride via hot filament assisted CVD and pulsed laser deposition, 1799
- Hot filament chemical vapor deposition**
- Preparation of crystalline carbon nitride films on silicon substrate by chemical vapor deposition, 635
- Hot filament CVD diamond deposition**
- Fabrication of integrated diamond cantilevers with tips for SPM applications, 906
- HPHT diamond**
- Diamond formation and wettability in a Mg–Cu–C system under high pressure and high temperature, 28
- HREM**
- HREM and EXELFS investigation of local structure in thin CVD diamond films, 758
- Hybrid r.f.-PLD technique**
- C-BN thin film formation in a hybrid r.f.-PLD technique, 599
- Hydrofluoric acid etching**
- Diamond nucleation enhancement by hydrofluoric acid etching of silicon substrate, 440
- Hydrogen**
- Hydrogen-related gap states in the near surface of chemical vapor deposited homoepitaxial diamond films, 303
  - Enhancement/depletion MESFETs of diamond and their logic circuits, 339
  - The roles of H and O atoms in diamond growth, 486
  - PACVD nano-crystalline B–C–N thin films obtained by use of an organoboron precursor, 608
  - Thermal-programmed desorption (TPD) of deuterium from  $\text{Di}(111)$  surface: presence of two adsorption states, 736
  - Etching of graphite and diamond by thermal energy hydrogen atoms, 787
  - Mechanism of surface smoothing of diamond by a hydrogen plasma, 791
  - Device modeling of high performance diamond MESFETs using p-type surface semiconductive layers, 865
  - Effects of remote hydrogen plasma treatment (RHPT) on ion-implanted CVD diamond, 1041
  - Hydrogen-, boron-, and hydrogen-boron-related low temperature photoluminescence of 6H-SiC, 1321

- Hydrogenated silicon carbon films**  
 a-SiC:H films deposited by PECVD from silane + acetylene and silane + acetylene + hydrogen gas mixture, 1606
- Hydrogenation**  
 Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226  
 Low frequency noise in silicon carbide Schottky diodes, 1494  
 Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- Hydrogen incorporation**  
 Hydrogen incorporation in epitaxial layers of 4H- and 6H-silicon carbide grown by vapor phase epitaxy, 1293
- Hysteresis loop**  
 Hysteresis loop in the current-voltage characteristic of Al/boron-doped polycrystalline diamond Schottky contact, 12
- Ib diamond**  
 Measurement of decay time for the NV centre in Ib diamond with a picosecond laser pulse, 1595
- ICP**  
 Diamond deposition and plasma diagnostics in a 27 MHz inductive coupled reactor (ICP), 1816
- Impact-ionization**  
 High field and high temperature stress of n-SiC MOS capacitors, 1489
- Impedance spectroscopy**  
 Insulating diamond coatings on tungsten electrodes, 293  
 An impedance spectroscopy investigation of polycrystalline diamond from dc to 1 GHz, 1689
- Implantation**  
 Ion beam assisted deposition of a tungsten compound layer on 6H-silicon carbide, 1432  
 Hafnium, cadmium and indium impurities in 4H-SiC observed by perturbed angular correlation spectroscopy, 1436
- Impurities**  
 Large-area diamond deposition by microwave plasma, 417  
 Distribution of the cobalt-related luminescence center in HPHT diamond, 708  
 Gap density of states in CVD diamond films from photoconductivity and photoluminescence data, 712  
 Capacitance-voltage measurements on metal-SiO<sub>2</sub>-boron-doped homoepitaxial diamond, 852
- In-diffusion**  
 Incorporation of lithium in single crystal diamond: diffusion profiles and optical and electrical properties, 1726
- In-situ**  
 In-situ ellipsometry study of initial stage of bias-enhanced nucleation and heteroepitaxy of diamond on silicon(100) by hot filament chemical vapor deposition, 1117
- In-situ X-ray diffraction under high pressure**  
 In-situ X-ray observation of phase transformation of rhombohedral boron nitride under static high pressure and high temperature, 1806
- Inclusions**  
 Stresses generated by inhomogeneous distributions of inclusions in diamonds, 120
- Infrared**  
 LWIR spectral properties of CVD diamond at cryogenic temperatures, 169  
 Diamond coatings for IR window applications, 386  
 Growth and characterisation of boron nitride films: layer sequence and phase identification, 594
- Infrared absorption**  
 Optical properties of nitrogen-rich carbon films deposited by d.c. magnetron sputtering, 33
- In situ molecular beam mass spectrometry**  
 Examination of the effects of nitrogen on the CVD diamond growth mechanism using in situ molecular beam mass spectrometry, 247
- Integrated circuit**  
 Total-dose hardness integrated circuit fabricated with silicon-on-diamond structured wafer, 673
- Integrated diamond cantilevers**  
 Fabrication of integrated diamond cantilevers with tips for SPM applications, 906
- Interface**  
 Transmission electron microscope study of heteroepitaxial diamond on Pt (111), 272  
 Modeling interface structures of cubic boron nitride films deposited heteroepitaxially and via a hexagonal boron nitride interlayer on silicon (001) surfaces, 589  
 Device modeling of high performance diamond MESFETs using p-type surface semiconductive layers, 865  
 Formation peculiarities of the interfacial structure during cBN wetting with Ag-Ti, Ag-Zr and Ag-Hf alloys, 931  
 Wafer warpage, crystal bending and interface properties of 4H-SiC epi-wafers, 1369  
 Structural and electrical properties of Schottky barriers on n-GaN, 1528  
 The crystallographic relationship of heteroepitaxial diamond films on scratched silicon substrates, 1836
- Interface/interfacial**  
 Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807  
 Carrier transport mechanisms through the metal/p-type diamond semiconductor interface, 847  
 Effect of substrate on the characteristics of the interface between diamond film and substrate, 959
- Interfacial**  
 Interfacial analysis of CVD diamond on copper substrates, 743
- Interfacial connectivity**  
 Topology of twin junctions in epitaxial  $\beta$ -SiC, 1362
- Interlayer**  
 Adhesion improvement of diamond films on steel substrates using chromium nitride interlayers, 796
- Internal field emission**  
 Internal field emission at metal/diamond contact and performance of thin film field emitters: computer simulation, 884
- Intrinsic stress**  
 Mechanisms of intrinsic stress generation in amorphous carbon thin films prepared by magnetron sputtering, 1182
- Ion-assisted deposition**  
 Growth and characterisation of boron nitride films: layer sequence and phase identification, 594  
 Preparation of CN<sub>x</sub> films by ion beam assisted filtered cathodic arc deposition, 626  
 DLC growth by ion beam assisted deposition: a molecular simulation, 1638  
 Near-edge X-ray absorption fine structure spectroscopy of arcjet-deposited cubic boron nitride, 1883
- Ion beam analysis**  
 Characterization of nucleation and growth of MW-CVD diamond films by spectroscopic ellipsometry and ion beam analysis methods, 1633
- Ion beam deposition**  
 Optical and photoemission studies of DLC films prepared with a systematic variation of the sp<sup>3</sup>:sp<sup>2</sup> composition, 687  
 Electronic and atomic structure of undoped and doped ta-C films, 830  
 Electrical properties and thermal stability of ion beam deposited BN thin films, 1129

- Ion beam growth**  
 Formation of nanocrystalline diamond by hydrocarbon plasma beam deposition, 255
- Ion beam modification**  
 Ion beam modification of tetrahedral amorphous carbon: the effect of irradiation temperature, 1622
- Ion bombardment**  
 Enhancement/depletion MESFETs of diamond and their logic circuits, 339  
 Phase stability and stress relaxation effects of cubic boron nitride thin films under 350 keV ion irradiation, 621  
 Low-temperature formation of  $\beta$ -silicon carbide, 645
- Ion implantation**  
 Characterization and growth of carbon phases synthesized by high temperature carbon ion implantation into copper, 261  
 High temperature polycrystalline diamond metal-insulator-semiconductor field-effect-transistor, 333  
 ESR studies of incorporation of phosphorus into high-pressure synthetic diamond, 356  
 Lift-off technique of homoepitaxial CVD diamond films by deep implantation and selective etching, 654  
 Effects of remote hydrogen plasma treatment (RHPT) on ion-implanted CVD diamond, 1041  
 SiC device technology: remaining issues, 1400  
 2.5 kV ion-implanted  $p^+n$  diodes in 6H-SiC, 1485
- Ion irradiation**  
 Transition from polymer-like to diamond-like a-C:H films. Structure and mechanical properties, 574
- Irradiation**  
 The irradiation and annealing of Si-doped diamond single crystals, 146
- Irradiation defects**  
 Radiation hardness of polycrystalline diamond, 314
- Irradiation temperature**  
 Ion beam modification of tetrahedral amorphous carbon: the effect of irradiation temperature, 1622
- IR reflectivity**  
 Infra-red characterization of carbonization of Si surfaces by gas source molecular beam epitaxy, 1772
- IR spectroscopy**  
 Investigation of the nucleation layer in c-BN film growth, 584
- Irvin curve**  
 The diamond Irvin curve, 308
- Isotopic effect**  
 Thermodynamic properties of  $^{13}\text{C}$ -diamond, 172
- JFET**  
 Temperature dependence of electrical properties of 6H-SiC buried gate JFET, 1504
- Junction termination extensions**  
 Numerical study of avalanche breakdown of 6H-SiC planar  $p-n$  junctions, 1500
- Kinetics**  
 Growth and doping via gas-source molecular beam epitaxy of SiC and SiC/AlN heterostructures and their microstructural and electrical characterization, 1282
- KVV deconvolution treatment**  
 Shock-wave-induced phase transition in C:N films, 640
- Langmuir probe**  
 Diamond deposition and plasma diagnostics in a 27 MHz inductive coupled reactor (ICP), 1816
- Large area deposition**  
 Transition from polymer-like to diamond-like a-C:H films. Structure and mechanical properties, 574
- Large Hadron Collider**  
 Neutron damage of CVD diamond, 353
- Laser**  
 Sequential multiple-laser-assisted polishing of free-standing CVD diamond substrates, 1789
- Laser ablation**  
 Production and characterisation of amorphic diamond films produced by pulsed laser ablation of graphite, 569
- Laser annealing**  
 Effects of thermal and laser annealing on silicon carbide nanopowder produced in radio frequency glow discharge, 1559
- Laser deposition**  
 Studies of nanoscale structure and its transformation in pulsed-laser deposited dense diamond-like carbon films, 564
- Lattice constant**  
 Thermodynamic properties of  $^{13}\text{C}$ -diamond, 172  
 Residual strains in GaN grown on 6H-SiC, 1524
- Lattice damage**  
 Liftoff-technique of single-crystal diamond plates: study of the lattice damage of the implanted substrates and the crystalline quality of the homoepitaxial films by ion channelling, 149
- Lattice defect**  
 Measurement of decay time for the NV centre in Ib diamond with a picosecond laser pulse, 1595
- Lattice perfection**  
 Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226  
 Low frequency noise in silicon carbide Schottky diodes, 1494  
 Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- Level sensor**  
 Insulating diamond coatings on tungsten electrodes, 293
- Light absorption**  
 Comparative study of optical absorption in diamond powders and polycrystalline CVD films, 1124
- Light device**  
 Spontaneous radiation in short period superlattices on the basis of carbon multilayer heterostructures, 1106
- Linear polarization**  
 Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17
- Liquid phase**  
 Growth of SiC from the liquid phase: wetting and dissolution of SiC, 1266
- Liquid phase epitaxy**  
 Overview of SiC power electronics, 1480
- Lithium**  
 Incorporation of lithium in single crystal diamond: diffusion profiles and optical and electrical properties, 1726
- Lithium in diamond films**  
 Lithium addition during CVD diamond deposition using lithium tert.-butanolat as precursor, 494
- Local structure**  
 HREM and EXELFS investigation of local structure in thin CVD diamond films, 758
- Low-energy electron diffraction**  
 Structure and morphology of SiC surfaces studied by LEED, AES, HREELS and STM, 1349
- Low defect films**  
 a-SiC:H films deposited by PECVD from silane + acetylene and silane + acetylene + hydrogen gas mixture, 1606
- Low pressure**  
 The formation of diamond from carbonyl material at ambient pressure, 1743

- Low temperature**
- Low-temperature deposition of optically transparent diamond using a low-pressure flat flame, 1862
- Low temperature photoluminescence**
- Radiation-induced defect centers in 4H silicon carbide, 1333
- LPCVD**
- Growth of SiC films obtained by LPCVD, 1306
- Luminescence**
- Nitrogen doping of diamond by ion implantation, 516
- Luminescence mapping**
- Raman and photoluminescence microscopy mapping of CVD micro-diamonds, 1587
- Machining**
- Characterization of metal–diamond interfaces: electron affinity and Schottky barrier height, 398
  - Characterization of the microstructure of diamond pyramidal microtip emitters, 403
  - Nanoscale grinding of ceramics using diamond fibres, 893
- Magnetron sputtering**
- Mechanisms of intrinsic stress generation in amorphous carbon thin films prepared by magnetron sputtering, 1182
- Mass density**
- Mechanisms of intrinsic stress generation in amorphous carbon thin films prepared by magnetron sputtering, 1182
- Mass spectrometry**
- Diamond growth chemistry: its observation using real time in situ molecular beam scattering techniques, 219
  - Investigations concerning the role of fluorine and chlorine in the low temperature growth of diamond, 964
- Mechanical integrity ratio**
- On the mechanical integrity ratio of diamond coatings, 348
- Mechanical properties**
- Diamond coatings for IR window applications, 386
  - Improvement of mechanical properties of a-C:H by silicon addition, 559
  - Transition from polymer-like to diamond-like a-C:H films. Structure and mechanical properties, 574
  - Mechanical properties of synthetic type IIa diamond crystal, 1841
- Membranes**
- Diamond membranes with controlled porosity, 1824
- Mesa diodes**
- Investigation of walk-out phenomena in SiC mesa diodes with  $\text{SiO}_2/\text{Si}_3\text{N}_4$  passivation, 1476
- MESFET**
- Microwave Power MESFET on 4H-SiC, 1508
  - The potential of SiC and GaN for application in high speed devices, 1512
- Metal**
- Enhancement/depletion MESFETs of diamond and their logic circuits, 339
  - Effects of  $\text{Mo}(\text{CO})_6$  and  $\text{W}(\text{CO})_6$  introduced to plasma on diamond synthesis by microwave plasma CVD, 501
  - Single source deposition of Me-C:H films using metal-organic precursors, 533
  - Carrier transport mechanisms through the metal/p-type diamond semiconductor interface, 847
- Metal–diamond interfaces**
- Characterization of metal–diamond interfaces: electron affinity and Schottky barrier height, 398
  - Characterization of the microstructure of diamond pyramidal microtip emitters, 403
- Metal–organic precursors**
- Growth of SiC films obtained by LPCVD, 1306
- Metal-oxide–semiconductor**
- High field and high temperature stress of n-SiC MOS capacitors, 1489
- Metallic solvent**
- Diamond formation and wettability in a Mg–Cu–C system under high pressure and high temperature, 28
- Metallization**
- Aluminium implantation of p-SiC for ohmic contacts, 1414
- Methane**
- Structure and properties of a-C:H films deposited onto polymeric substrates, 551
- Methyl**
- Spatially resolved measurements of absolute  $\text{CH}_3$  concentration in a hot-filament reactor, 476
- Micro-inclusions**
- Observation of micro-inclusions in diamond by scanning X-ray analytical microscope, 1680
- Micro analysis systems**
- Colour sensing applications of hydrogenated amorphous silicon carbide, 1542
- Microhardness**
- Nitrogen and iodine doping in amorphous diamond-like carbon films, 555
- Microparticle**
- The formation of diamond from carbonyl material at ambient pressure, 1743
- Micropipes**
- The kinetic growth model applied to micropipes in 6H-SiC, 1269
  - Micropipe defects and voids at  $\beta\text{-SiC}/\text{Si}(100)$  interfaces, 1365
  - SiC device technology: remaining issues, 1400
- Microscopic analysis**
- Insight on the microscopical structure of a-C and a-C:H thin films through electron spin resonance analysis, 725
- Microstructural evolution**
- Effects of processing conditions on the growth of nanocrystalline diamond thin films: real time spectroscopic ellipsometry studies, 55
- Microstructure**
- Optical properties and microstructure of CVD diamond films, 153
  - Nanocrystalline diamond films: transmission electron microscopy and Raman spectroscopy characterization, 159
  - Characterization and growth of carbon phases synthesized by high temperature carbon ion implantation into copper, 261
  - Transmission electron microscope study of heteroepitaxial diamond on Pt (111), 272
  - Characterization of metal–diamond interfaces: electron affinity and Schottky barrier height, 398
  - Characterization of the microstructure of diamond pyramidal microtip emitters, 403
  - Effect of negative bias voltage on a-C:H films deposited in electron cyclotron resonance plasma, 542
  - Studies of nanoscale structure and its transformation in pulsed-laser deposited dense diamond-like carbon films, 564
  - CBN–TiH<sub>2</sub> composites: chemical equilibria, microstructure and mechanical studies, 1192
  - Thermal gas effusion from diamond-like carbon films, 1830
- Microtwins development**
- Growth of SiC films obtained by LPCVD, 1306
- Microwave**
- Investigations concerning the role of fluorine and chlorine in the low temperature growth of diamond, 964
- Microwave electrode discharge**
- Diamond deposition in a microwave electrode discharge at reduced pressures, 224
- Microwave plasma**
- Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17

- Microwave plasma-assisted chemical vapor deposition  
H actinometry with  $\text{CF}_4$  addition in microwave plasma-assisted chemical vapor deposition of diamond, 472
- Improvement of diamond nuclei orientation by double-step bias treatment in microwave plasma-assisted chemical vapor deposition using  $\text{C}_2\text{H}_4$  and  $\text{CH}_4$  as carbon source, 668
- Microwave plasma-assisted CVD  
Optical and electrical investigation of boron-doped homoepitaxial diamond, 835
- Microwave plasma-enhanced CVD  
Effects of processing conditions on the growth of nanocrystalline diamond thin films: real time spectroscopic ellipsometry studies, 55
- Microwave power  
Silicon carbide for microwave power applications, 1405
- Microwave power effects  
Microwave power effects on the properties of phosphorus-doped SiC:H films prepared using ECR-CVD, 48
- Microwave reactor  
An experimental study of high pressure synthesis of diamond films using a microwave cavity plasma reactor, 1097
- Misorientation angles  
A study on surface morphologies of (001) homoepitaxial diamond films, 130
- MIS structures  
Amorphous  $\text{GaAs}_{1-x}\text{N}_x$  thin films on crystalline Si substrates: growth and characterizations, 1568
- Mobility  
The drift mobility and decay of photocurrent in doped amorphous diamond-like carbon films, 1152
- Temperature dependence of electrical properties of 6H-SiC buried gate JFET, 1504
- Electrical properties of B-doped homoepitaxial diamond (001) film, 1753
- MOCVD  
SiC and group III nitride growth in MOVPE production reactors, 1301
- Modeling  
Spatially resolved measurements of absolute  $\text{CH}_3$  concentration in a hot-filament reactor, 476
- Growth and characterisation of boron nitride films: layer sequence and phase identification, 594
- Device modeling of high performance diamond MESFETs using p-type surface semiconductive layers, 865
- Simulation of morphological instabilities during diamond chemical vapor deposition, 1759
- Modelling  
SiC and group III nitride growth in MOVPE production reactors, 1301
- Modified silica glass substrates  
Features of diamond deposition on modified silica glass substrates, 444
- Molecular beam epitaxy  
Growth and doping via gas-source molecular beam epitaxy of SiC and SiC/AlN heterostructures and their microstructural and electrical characterization, 1282
- Chemical conversion of Si to SiC by solid source MBE and RTCVD, 1311
- Hexagonal and cubic SiC thin films on SiC deposited by solid source MBE, 1316
- Molecular structure  
Molecular structure of E-BN, 617
- Molybdenum plate  
Diamond growth in a direct-current low-pressure supersonic plasmajet, 406
- Molybdenum virgin film  
A two-step process for the formation of a  $\text{Mo}_2\text{C}$  contact on polycrystalline diamond films, 843
- Morphology  
Diamond formation and wettability in a Mg–Cu–C system under high pressure and high temperature, 28
- Pressure Dependence of Growth Mode of HFCVD Diamond, 81
- On the development of CVD diamond film morphology due to the twinning on {111} surfaces, 435
- Effect of surface species concentrations and temperature on diamond film morphology in inductively coupled r.f. plasma CVD, 481
- Morphologies of diamond films from atomic-scale simulations of chemical vapor deposition, 1198
- Growth of SiC from the liquid phase: wetting and dissolution of SiC, 1266
- Structure and morphology of SiC surfaces studied by LEED, AES, HREELS and STM, 1349
- Morphology evolution  
Simulation of morphological instabilities during diamond chemical vapor deposition, 1759
- MOS-structure  
“Carbon cluster model” for electronic states at SiC/SiO<sub>2</sub> interfaces, 1472
- MOSFET  
Passivation of interface traps in MOS-Devices on n- and p-type 6H-SiC, 1497
- Multilayers  
Experimental and theoretical studies of growth mechanisms of hard wear-resistant carbon-based films on three-dimensional substrates, 970
- MW-CVD diamond  
Characterization of nucleation and growth of MW-CVD diamond films by spectroscopic ellipsometry and ion beam analysis methods, 1633
- MW-PACVD  
Optimization of MW-PACVD diamond deposition parameters for high nucleation density and growth rate on  $\text{Si}_3\text{N}_4$  substrate, 411
- n-type conduction  
Incorporation of lithium in single crystal diamond: diffusion profiles and optical and electrical properties, 1726
- Nanocrystalline diamond  
Effects of processing conditions on the growth of nanocrystalline diamond thin films: real time spectroscopic ellipsometry studies, 55
- Nanoparticles  
Effects of thermal and laser annealing on silicon carbide nanopowder produced in radio frequency glow discharge, 1559
- Natural diamond  
A micro-IBIC comparison between natural and CVD diamond, 320
- Negative-electron-affinity  
Comparative study of excitonic recombination radiation from diamonds grown by CVD and HP/HT methods, 1668
- Neutron damage  
Neutron damage of CVD diamond, 353
- New absorption line  
The 0.545 eV center in neutron irradiated and annealed type Ib diamond, 1722
- NEXAFS  
Near-edge X-ray absorption fine structure spectroscopy of arcjet-deposited cubic boron nitride, 1883

- Nitride**
- Formation of cubic boron nitride thin films by reactive cathodic arc evaporation, 1005
  - SiC and group III nitride growth in MOVPE production reactors, 1301
- Nitrides**
- Adhesion improvement of diamond films on steel substrates using chromium nitride interlayers, 796
- III-V nitrides**
- Thermodynamics and high-pressure growth of (Al, Ga, In)N single crystals, 1515
- Nitrogen**
- Optical properties of nitrogen-rich carbon films deposited by d.c. magnetron sputtering, 33
  - Effect of nitrogen concentration on plasma reactivity and diamond growth in a H<sub>2</sub>-CH<sub>4</sub>-N<sub>2</sub> microwave discharge, 107
  - Examination of the effects of nitrogen on the CVD diamond growth mechanism using *in situ* molecular beam mass spectrometry, 247
  - Combined effect of nitrogen and pulsed microwave plasma on diamond growth, 505
  - Hard a-C(N):H films obtained from plasma decomposition of methylamine-containing mixtures, 631
  - Investigation of lattice impurities and photochromic centres in diamond with high resolution positron annihilation spectroscopy, 1777
- Nitrogen addition**
- Effects of simultaneous boron and nitrogen addition on hot-filament CVD diamond growth, 456
- Nitrogen aggregation**
- The aggregation of nitrogen and the formation of A centres in diamonds, 1643
- Nitrogen donors**
- Sublimation growth of 4H- and 6H-SiC boule crystals, 1262
- Nitrogen implantation**
- Nitrogen doping of diamond by ion implantation, 516
- Non-diamond carbon**
- Optical properties of nitrogen-rich carbon films deposited by d.c. magnetron sputtering, 33
- Nondestructive testing**
- Nonlinear optical mapping of 3C-inclusions in 6H-SiC-epilayers, 1374
- Nonuniform**
- Stresses generated by inhomogeneous distributions of inclusions in diamonds, 120
- Nozzles**
- Cylindrically symmetric diamond parts by hot-filament CVD, 1707
- Nucleation**
- Formation of nanocrystalline diamond by hydrocarbon plasma beam deposition, 255
  - Formation of an oriented β-SiC layer during the initial growth phase of diamond on silicon (100), 282
  - Diamond growth on a large area and some aspects of diamond nucleation, 426
  - Initial results of a novel pre-deposition seeding technique for achieving an ultra-high nucleation density for CVD diamond growth, 430
  - Investigation of the nucleation layer in c-BN film growth, 584
  - Biased enhanced nucleation of diamond on metals: an OES and electrical investigation, 658
  - AES and XPS observations of HFCVD diamond deposition on monocrystalline (111) copper, 664
  - Formation mechanisms of diamond precursors during the nucleation process, 1047
- Characterization of nucleation and growth of MW-CVD diamond films by spectroscopic ellipsometry and ion beam analysis methods, 1633**
- Nucleation enhancement behavior of diamond on Si substrate according to surface treatment materials, 1716**
- Nucleation time**
- The effect of ultrasonic vibration on CVD diamond nucleation, 1031
- Nuclei**
- Stresses generated by inhomogeneous distributions of inclusions in diamonds, 120
- NV centre**
- Measurement of decay time for the NV centre in Ib diamond with a picosecond laser pulse, 1595
- OBIC**
- OBIC studies on 6H-SiC Schottky rectifiers with different surface pretreatments, 1396
  - 2.5 kV ion-implanted p<sup>+</sup>n diodes in 6H-SiC, 1485
- ODMR**
- Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers, 1381
- Ohmic contact**
- Aluminium implantation of p-SiC for ohmic contacts, 1414
- Ohmic contacts**
- TEM study of Ni and Ni<sub>2</sub>Si ohmic contacts to SiC, 1428
- Optical**
- LWIR spectral properties of CVD diamond at cryogenic temperatures, 169
  - Nitrogen and iodine doping in amorphous diamond-like carbon films, 555
  - Optical properties of diamond film deposited by CVD of Freon: studies on mechanical properties from the absorption band tail, 991
- Optical/electrical investigation**
- Optical and electrical investigation of boron-doped homoepitaxial diamond, 835
- Optical absorption**
- Quantitative study of Raman scattering and defect optical absorption in CVD diamond films, 704
  - Optical and electrical characteristics of amorphous diamond films, 983
- Optical constants**
- Optical properties and microstructure of CVD diamond films, 153
- Optical emission spectroscopy**
- Effect of nitrogen concentration on plasma reactivity and diamond growth in a H<sub>2</sub>-CH<sub>4</sub>-N<sub>2</sub> microwave discharge, 107
  - Energy distribution of H atom and C<sub>2</sub> radical during diamond growth in H<sub>2</sub>/Ar-CH<sub>4</sub>-O<sub>2</sub> plasma, 468
- Optical properties**
- Optical properties of nitrogen-rich carbon films deposited by d.c. magnetron sputtering, 33
  - Optical and photoemission studies of DLC films prepared with a systematic variation of the sp<sup>3</sup>:sp<sup>2</sup> composition, 687
- Optical reflectivity**
- Optimising control of microwave plasma bias enhanced nucleation for heteroepitaxial chemical vapour deposition diamond, 676
- Optimization method**
- Optimization of MW-PACVD diamond deposition parameters for high nucleation density and growth rate on Si<sub>3</sub>N<sub>4</sub> substrate, 411
- Optoelectronic properties**
- Photoelectrical characteristics of diamond UV detectors: dependence on device design and film quality, 361
  - Photoconductive properties of thin film diamond, 374

- Atomic hydrogen-induced chemical vapor deposition of a-Si:C:H thin-film materials from alkylsilane precursors, 1081
- Optoelectronics**
- Thermodynamics and high-pressure growth of (Al, Ga, In)N single crystals, 1515
  - Colour sensing applications of hydrogenated amorphous silicon carbide, 1542
- Orientation**
- Formation of an oriented  $\beta$ -SiC layer during the initial growth phase of diamond on silicon (100), 282
  - A multilayer approach to high adhesion diamond-like carbon coatings on titanium, 802
  - Oriented diamond growth on platinum via a metal–carbon–hydrogen low-pressure processing route, 1747
- Orthopaedic implants**
- Evaluation of diamond-like carbon-coated orthopaedic implants, 390
- Oxidation behaviour**
- High temperature Young's modulus of polycrystalline diamond, 344
- Oxide interface**
- SiC device technology: remaining issues, 1400
- Oxide passivation**
- Investigation of walk-out phenomena in SiC mesa diodes with  $\text{SiO}_2/\text{Si}_3\text{N}_4$  passivation, 1476
- Oxygen**
- The roles of H and O atoms in diamond growth, 486
  - Reactive ion etching of diamond as a means of enhancing chemically-assisted mechanical polishing efficiency, 952
- P-type diamond films**
- Piezoresistive property of CVD diamond films, 367
- PAC**
- Hafnium, cadmium and indium impurities in 4H-SiC observed by perturbed angular correlation spectroscopy, 1436
- Paramagnetic defect**
- Electronic structure of diamond-like carbon, 212
- PAS**
- Comparative study of optical absorption in diamond powders and polycrystalline CVD films, 1124
- Passivation**
- Passivation of interface traps in MOS-Devices on *n*- and *p*-type 6H-SiC, 1497
- Pd**
- Diamond deposition on noble metals, 240
- Phase transition**
- Investigation of the c-BN/h-BN phase transformation at normal pressure, 286
- Phase transition shock wave compression**
- Shock-wave-induced phase transition in C:N films, 640
- Phosphorous**
- Nuclear transmutation doping of 6H-silicon carbide with phosphorous, 1440
- Phosphorus**
- ESR studies of incorporation of phosphorus into high-pressure synthetic diamond, 356
- Phosphorus-doped SiC:H films**
- Microwave power effects on the properties of phosphorus-doped SiC:H films prepared using ECR-CVD, 48
- Phosphorus doping**
- Electron emission characteristics of metal/diamond field emitters, 889
- Photoacoustic spectroscopy**
- Comparative study of optical absorption in diamond powders and polycrystalline CVD films, 1124
- Photoconductivity**
- Photoelectrical characteristics of diamond UV detectors: dependence on device design and film quality, 361
  - Photoconductive properties of thin film diamond, 374
  - Gap density of states in CVD diamond films from photoconductivity and photoluminescence data, 712
  - The drift mobility and decay of photocurrent in doped amorphous diamond-like carbon films, 1152
  - Photoconductivity of CVD diamond under bandgap and subbandgap irradiations, 1157
  - Influence of nitrogen doping on photoconductivity properties of a: DLC films, 1868
- Photodetector**
- Photoconductive properties of thin film diamond, 374
- Photoelectrical**
- Electrical conduction in polycrystalline diamond and the effects of UV irradiation, 860
- Photoelectrical devices**
- Photoelectrical characteristics of diamond UV detectors: dependence on device design and film quality, 361
- Photoelectron emission**
- Excimer laser-induced electron emission from diamond films, 1650
- Photoelectron spectroscopy**
- Electronic and structural properties of the interface between c-Si(111) and diamond-like carbon, 730
  - Angle resolved photoemission and the band structure of 6H-SiC, 1358
  - Surface chemistry of 6H-SiC(000 $\bar{l}$ ) after reactive ion etching, 1451
- Photoemission**
- Optical and photoemission studies of DLC films prepared with a systematic variation of the  $\text{sp}^3:\text{sp}^2$  composition, 687
- Photoluminescence**
- Photoluminescence in hydrogenated amorphous Carbon, 700
  - Distribution of the cobalt-related luminescence center in HPHT diamond, 708
  - Gap density of states in CVD diamond films from photoconductivity and photoluminescence data, 712
  - The optical characterization of boron-doped MPCVD diamond films, 940
  - Effects of remote hydrogen plasma treatment (RHPT) on ion-implanted CVD diamond, 1041
  - High quality 4H-SiC grown on various substrate orientations, 1289
  - Hydrogen-, boron-, and hydrogen-boron-related low temperature photoluminescence of 6H-SiC, 1321
  - Deep luminescent centres in electron-irradiated 6H SiC, 1378
  - Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers, 1381
  - Nuclear transmutation doping of 6H-silicon carbide with phosphorous, 1440
  - Emission and excitation spectra of silicon-related luminescent centers in CVD-grown diamond films, 1564
- Photothermal deflection spectroscopy**
- Incorporation of lithium in single crystal diamond: diffusion profiles and optical and electrical properties, 1726
- Physical vapor deposition**
- DLC growth by ion beam assisted deposition: a molecular simulation, 1638
- Physical vapour deposition**
- Formation of cubic boron nitride thin films by reactive cathodic arc evaporation, 1005
- Piezoresistive effect**
- Piezoresistive property of CVD diamond films, 367
- Planar defects**
- Topology of twin junctions in epitaxial  $\beta$ -SiC, 1362

**Plasma**

- Low pressure polymer precursor process for synthesis of hard glassy carbon and diamond films, 230  
Effect of surface species concentrations and temperature on diamond film morphology in inductively coupled r.f. plasma CVD, 481  
PACVD nano-crystalline B-C-N thin films obtained by use of an organoboron precursor, 608  
Mechanism of surface smoothing of diamond by a hydrogen plasma, 791  
Atomic hydrogen-induced chemical vapor deposition of a-Si:C:H thin-film materials from alkylsilane precursors, 1081

**Plasma-enhanced chemical vapour deposition**

- Influence of process parameters on the size of the bias-nucleated area for diamond deposition with plasma-enhanced chemical vapour deposition, 6

**Plasma diagnostics**

- Effects of Mo(CO)<sub>6</sub> and W(CO)<sub>6</sub> introduced to plasma on diamond synthesis by microwave plasma CVD, 501

**Plasma enhanced chemical vapour deposition**

- a-SiC:H films deposited by PECVD from silane + acetylene and silane + acetylene + hydrogen gas mixture, 1606

**Plasma processing**

- An experimental study of high pressure synthesis of diamond films using a microwave cavity plasma reactor, 1097

**Plastic deformation**

- How plastic deformation can produce texture in graphitic films of boron nitride, carbon nitride, and carbon, 1219

**Platinum**

- Heteroepitaxial diamond growth process on platinum (111), 266  
pn-junction

- Nuclear transmutation doping of 6H-silicon carbide with phosphorous, 1440

**Polarized IR reflection spectroscopy**

- Optical study of boron nitride thin films prepared by plasma-enhanced chemical vapor deposition, 1550

**Polished silicon**

- Influence of process parameters on the size of the bias-nucleated area for diamond deposition with plasma-enhanced chemical vapour deposition, 6

**Poly-SiC**

- Growth of SiC films obtained by LPCVD, 1306

**Polycrystalline**

- Elastic properties of polycrystalline cubic boron nitride and diamond by dynamic resonance measurements, 812

- Enhancing low field electron emission from polycrystalline diamond, 869

- The measurement of thermal properties of diamond, 1057

- Oriented diamond growth on platinum via a metal-carbon-hydrogen low-pressure processing route, 1747

**Polycrystalline diamond**

- The diamond Irvin curve, 308

- Radiation hardness of polycrystalline diamond, 314

- High temperature Young's modulus of polycrystalline diamond, 344

- Measurement and calculation of the thermal expansion coefficient of diamond, 839

**Polymer precursor**

- Low pressure polymer precursor process for synthesis of hard glassy carbon and diamond films, 230

**Polytypism**

- Chemical conversion of Si to SiC by solid source MBE and RTCVD, 1311

**Porous Si**

- Diamond seed incorporation by electrochemical treatment of silicon substrate, 1629

**Positron Spectroscopy**

- Investigation of lattice impurities and photochromic centres in diamond with high resolution positron annihilation spectroscopy, 1777

**Post-deposition processing**

- Sequential multiple-laser-assisted polishing of free-standing CVD diamond substrates, 1789

**Post implantation annealing**

- Investigation of the effects of high temperature implantation and post implantation annealing on the electrical behavior of nitrogen implanted  $\beta$ -SiC films, 1445

**Powder**

- Effects of thermal and laser annealing on silicon carbide nanopowder produced in radio frequency glow discharge, 1559

**Power and microwave characteristics**

- Microwave Power MESFET on 4H-SiC, 1508

**Power semiconductor devices**

- Overview of SiC power electronics, 1480

**Pre-deposition processing**

- Fabrication of high-quality oxides on SiC by remote PECVD, 1420

**Pre-treated substrates**

- Initial results of a novel pre-deposition seeding technique for achieving an ultra-high nucleation density for CVD diamond growth, 430

**Preferential**

- Preferential etching of SiC crystals, 1456

**Pretreated substrates**

- Tuning the electron affinity of CVD diamond with adsorbed caesium and oxygen layers, 874

- Nucleation enhancement behavior of diamond on Si substrate according to surface treatment materials, 1716

**Processing**

- Enhancing low field electron emission from polycrystalline diamond, 869

- Tetrahedral amorphous carbon (ta-C) coatings for processing tools to reduce contamination in the analysis of trace elements, 1207

**Process parameters**

- Influence of process parameters on the size of the bias-nucleated area for diamond deposition with plasma-enhanced chemical vapour deposition, 6

**Prostheses**

- A multilayer approach to high adhesion diamond-like carbon coatings on titanium, 802

**Protection**

- On the mechanical integrity ratio of diamond coatings, 348

**Pt**

- Diamond deposition on noble metals, 240

**Pulsed cathodic arc discharge**

- On correlation between the shape of Raman spectra and short-range order structure of hydrogen-free amorphous carbon films, 1026

**Pulsed laser deposition**

- Growth of AlN thin films on (111) and (100) silicon by pulsed laser deposition in nitrogen plasma ambient, 1015

- Deposition of carbon nitride via hot filament assisted CVD and pulsed laser deposition, 1799

**Pulsed microwave discharge**

- Combined effect of nitrogen and pulsed microwave plasma on diamond growth, 505

**Quantitative measurement**

- On the mechanical integrity ratio of diamond coatings, 348

- Radiation**
- Spontaneous radiation in short period superlattices on the basis of carbon multilayer heterostructures, 1106
- Radiation-induced deep defect centers**
- Radiation-induced defect centers in 4H silicon carbide, 1333
- Radiation hardness**
- Radiation hardness of polycrystalline diamond, 314
  - Total-dose hardness integrated circuit fabricated with silicon-on-diamond structured wafer, 673
- Radical**
- Diamond growth chemistry: its observation using real time in situ molecular beam scattering techniques, 219
- Radical temperature**
- Energy distribution of H atom and C<sub>2</sub> radical during diamond growth in H<sub>2</sub>/Ar-CH<sub>4</sub>-O<sub>2</sub> plasma, 468
- Raman**
- Lithium addition during CVD diamond deposition using lithium tert.-butanolat as precursor, 494
  - Investigation of the boron incorporation in polycrystalline CVD diamond films by TEM, EELS and Raman spectroscopy, 763
- Raman/photoluminescence spectroscopy**
- Radiation hardness of polycrystalline diamond, 314
- Raman mapping**
- Raman and photoluminescence microscopy mapping of CVD micro-diamonds, 1587
- Raman scattering**
- Quantitative study of Raman scattering and defect optical absorption in CVD diamond films, 704
- Raman spectroscopy**
- Effect of nitrogen concentration on plasma reactivity and diamond growth in a H<sub>2</sub>-CH<sub>4</sub>-N<sub>2</sub> microwave discharge, 107
  - Nanocrystalline diamond films: transmission electron microscopy and Raman spectroscopy characterization, 159
  - Enhanced deposition rate of diamond in atmospheric pressure plasma CVD: effects of a secondary discharge, 202
  - Large-area diamond deposition by microwave plasma, 417
  - Combined effect of nitrogen and pulsed microwave plasma on diamond growth, 505
  - C-BN thin film formation in a hybrid r.f.-PLD technique, 599
  - Raman spectroscopy investigation of cubic boron nitride single crystals and layers on Si(100), 612
  - Preparation of CN<sub>x</sub> films by ion beam assisted filtered cathodic arc deposition, 626
  - Lift-off technique of homoepitaxial CVD diamond films by deep implantation and selective etching, 654
  - Raman diagnostics of amorphous diamond-like carbon films produced with a mass-separated ion beam, 694
  - Evaluation of MPCVD diamond film adhesion on hard metal substrates by micro Raman spectroscopy, 769
  - Investigations concerning the role of fluorine and chlorine in the low temperature growth of diamond, 964
  - On correlation between the shape of Raman spectra and short-range order structure of hydrogen-free amorphous carbon films, 1026
  - The effect of ultrasonic vibration on CVD diamond nucleation, 1031
  - Calculation of the stress in large square facets of MPCVD grown diamond from cathodoluminescence and raman spectroscopy measurements and comparison to stress predicted from finite element models, 1062
  - Sequential multiple-laser-assisted polishing of free-standing CVD diamond substrates, 1789
  - Low-temperature deposition of optically transparent diamond using a low-pressure flat flame, 1862
- Rare-gas based plasma**
- Energy distribution of H atom and C<sub>2</sub> radical during diamond growth in H<sub>2</sub>/Ar-CH<sub>4</sub>-O<sub>2</sub> plasma, 468
- Reactive ion etching**
- Surface chemistry of 6H-SiC(000 $\bar{I}$ ) after reactive ion etching, 1451
  - Schottky contact investigation on reactive ion etched 6H  $\alpha$ -SiC, 1459
- Reactive ion plasma**
- Reactive ion etching of diamond as a means of enhancing chemically-assisted mechanical polishing efficiency, 952
- Real time spectroscopic ellipsometry**
- Effects of processing conditions on the growth of nanocrystalline diamond thin films: real time spectroscopic ellipsometry studies, 55
- Reduced pressure**
- Diamond deposition in a microwave electrode discharge at reduced pressures, 224
- Reflection high energy electron diffraction**
- Chemical conversion of Si to SiC by solid source MBE and RTCVD, 1311
- Remote PECVD**
- Fabrication of high-quality oxides on SiC by remote PECVD, 1420
- Residual strains**
- Residual strains in GaN grown on 6H-SiC, 1524
- Residual stress**
- Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807
  - Stiffness, residual stresses and interfacial fracture energy of diamond films on titanium, 1612
- Resistivity**
- The diamond Irvin curve, 308
  - High field/high temperature performance of semi-insulating silicon carbide, 1392
- Response surface methodology**
- Characterization and optimization of mid-frequency plasma-enhanced chemical vapour deposited carbon films using response surface methodology, 537
- Review**
- Progress in the study of optical and related properties of SiC since 1992, 1243
- R.f.**
- Effect of surface species concentrations and temperature on diamond film morphology in inductively coupled r.f. plasma CVD, 481
- R.f. CVD**
- Hard a-C(N):H films obtained from plasma decomposition of methylamine-containing mixtures, 631
- R.f. Plasma CVD**
- Optical study of boron nitride thin films prepared by plasma-enhanced chemical vapor deposition, 1550
- RHEED**
- A study on surface morphologies of (001) homoepitaxial diamond films, 130
- Rhenium**
- An interface study of vapor-deposited rhenium with the two (0001) polar faces of single crystal 6H-SiC, 1424
- Rhombohedral boron nitride**
- In-situ X-ray observation of phase transformation of rhombohedral boron nitride under static high pressure and high temperature, 1806
- RIE**
- Comparative investigation of ECR-RIE patterns on Si and C faces of 6H-SiC using a CF<sub>4</sub>/O<sub>2</sub> gas mixture, 1463

- Roman mapping  
 Raman and photoluminescence microscopy mapping of CVD micro-diamonds, 1587
- Roughness  
 Optical properties and microstructure of CVD diamond films, 153  
 Optical investigation of thick 3C-SiC layers deposited on bulk silicon by CVD, 1385
- Rutherford backscattering spectrometry  
 Anisotropic oxidation of silicon carbide, 1467
- Scanning force microscopy  
 The kinetic growth model applied to micropipes in 6H-SiC, 1269
- Scanning X-ray analytical microscope  
 Observation of micro-inclusions in diamond by scanning X-ray analytical microscope, 1680
- Schottky barrier  
 Structural and electrical properties of Schottky barriers on n-GaN, 1528
- Schottky barrier height  
 Characterization of metal-diamond interfaces: electron affinity and Schottky barrier height, 398  
 Characterization of the microstructure of diamond pyramidal microtip emitters, 403
- Schottky contact  
 Hysteresis loop in the current-voltage characteristic of Al/boron-doped polycrystalline diamond Schottky contact, 12
- Schottky contacts  
 OBIC studies on 6H-SiC Schottky rectifiers with different surface pretreatments, 1396  
 Schottky contact investigation on reactive ion etched 6H  $\alpha$ -SiC, 1459
- Schottky diode  
 High-voltage Schottky diode on epitaxial diamond layer, 329  
 Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226  
 Low frequency noise in silicon carbide Schottky diodes, 1494  
 Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- Schottky diodes  
 SiC device technology: remaining issues, 1400
- Second harmonic generation  
 Nonlinear optical mapping of 3C-inclusions in 6H-SiC-epilayers, 1374
- Seeding  
 Initial results of a novel pre-deposition seeding technique for achieving an ultra-high nucleation density for CVD diamond growth, 430
- Si-doped diamond  
 The irradiation and annealing of Si-doped diamond single crystals, 146
- SiC  
 Diamond deposition from halogenated methane precursors on Si and SiC substrates, 85  
 The origin of 3C polytype inclusions in epitaxial layers of silicon carbide grown by chemical vapour deposition, 1297  
 SiC and group III nitride growth in MOVPE production reactors, 1301  
 Hydrogen-, boron-, and hydrogen-boron-related low temperature photoluminescence of 6H-SiC, 1321  
 Carrier lifetimes in SiC, studied by time resolved photoluminescence spectroscopy, 1324  
 Thermal properties of  $\beta$ -SiC epitaxial layers between 150 C and 500 C measured by using microstructures, 1338  
 Deep luminescent centres in electron-irradiated 6H SiC, 1378  
 SiC device technology: remaining issues, 1400
- Nuclear transmutation doping of 6H-silicon carbide with phosphorous, 1440  
 Preferential etching of SiC crystals, 1456  
 Comparative investigation of ECR-RIE patterns on Si and C faces of 6H-SiC using a CF<sub>4</sub>/O<sub>2</sub> gas mixture, 1463  
 Passivation of interface traps in MOS-Devices on *n*- and *p*-type 6H-SiC, 1497
- $\beta$ -SiC  
 Analysis of transport properties of  $\beta$ -SiC films: determination of donor density and compensation ratio, 1329  
 Investigation of the effects of high temperature implantation and post implantation annealing on the electrical behavior of nitrogen implanted  $\beta$ -SiC films, 1445
- $\beta$ -SiC on SOI  
 $\beta$ -SiC films on SOI substrates for high temperature applications, 1448
- SiCOI  
 $\beta$ -SiC films on SOI substrates for high temperature applications, 1448
- SiC polytypes  
 Sublimation growth of 4H- and 6H-SiC boule crystals, 1262
- SiC substrates  
 Growth, doping and characterization of Al<sub>x</sub>Ga<sub>1-x</sub>N thin film alloys on 6H-SiC(0001) substrates, 196
- SiC thin films  
 Optically detected magnetic resonance studies of defects in 3C SiC epitaxial layers, 1381
- SiC vapor phase epitaxy  
 Hydrogen incorporation in epitaxial layers of 4H- and 6H-silicon carbide grown by vapor phase epitaxy, 1293
- SiC/SiO<sub>2</sub>-interface  
 "Carbon cluster model" for electronic states at SiC/SiO<sub>2</sub> interfaces, 1472
- Silicon  
 Crystalline quality of highly oriented diamond films grown on <100> silicon studied by conventional TEM, 41  
 Mechanisms of CVD diamond nucleation and growth on mechanically scratched and virgin Si(100) surfaces, 235  
 Modeling interface structures of cubic boron nitride films deposited heteroepitaxially and via a hexagonal boron nitride interlayer on silicon (001) surfaces, 589  
 Diamond nucleation on silicon during bias treatment in chemical vapour deposition as analysed by electron microscopy, 747
- Silicon carbide  
 Mechanisms of CVD diamond nucleation and growth on mechanically scratched and virgin Si(100) surfaces, 235  
 Formation of an oriented  $\beta$ -SiC layer during the initial growth phase of diamond on silicon (100), 282  
 Low-temperature formation of  $\beta$ -silicon carbide, 645  
 Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226  
 Progress in the study of optical and related properties of SiC since 1992, 1243  
 Defects formation in sublimation grown 6H-SiC single crystal boules, 1249  
 Growth of SiC from the liquid phase: wetting and dissolution of SiC, 1266  
 Growth and doping via gas-source molecular beam epitaxy of SiC and SiC/AlN heterostructures and their microstructural and electrical characterization, 1282  
 Chemical conversion of Si to SiC by solid source MBE and RTCVD, 1311  
 Hexagonal and cubic SiC thin films on SiC deposited by solid source MBE, 1316  
 Polytypism and surface structure of SiC, 1346

- Structure and morphology of SiC surfaces studied by LEED, AES, HREELS and STM, 1349  
 Micropipe defects and voids at  $\beta$ -SiC/Si(100) interfaces, 1365  
 High field/high temperature performance of semi-insulating silicon carbide, 1392  
 Silicon carbide for microwave power applications, 1405  
 Fabrication of high-quality oxides on SiC by remote PECVD, 1420  
 An interface study of vapor-deposited rhenium with the two (0001) polar faces of single crystal 6H-SiC, 1424  
 TEM study of Ni and Ni<sub>2</sub>Si ohmic contacts to SiC, 1428  
 Ion beam assisted deposition of a tungsten compound layer on 6H-silicon carbide, 1432  
 Hafnium, cadmium and indium impurities in 4H-SiC observed by perturbed angular correlation spectroscopy, 1436  
 Surface chemistry of 6H-SiC(000 $\bar{I}$ ) after reactive ion etching, 1451  
 Schottky contact investigation on reactive ion etched 6H  $\alpha$ -SiC, 1459  
 Anisotropic oxidation of silicon carbide, 1467  
 Overview of SiC power electronics, 1480  
 High field and high temperature stress of n-SiC MOS capacitors, 1489  
 Low frequency noise in silicon carbide Schottky diodes, 1494  
 Microwave Power MESFET on 4H-SiC, 1508  
 Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547  
 Effects of thermal and laser annealing on silicon carbide nanopowder produced in radio frequency glow discharge, 1559
- Silicon on diamond**  
 Total-dose hardness integrated circuit fabricated with silicon-on-diamond structured wafer, 673
- Silicon substrate**  
 Diamond nucleation enhancement by hydrofluoric acid etching of silicon substrate, 440  
 Preparation of crystalline carbon nitride films on silicon substrate by chemical vapor deposition, 635
- (001) silicon substrates  
 TEM investigations on the heteroepitaxial nucleation of CVD diamond on (001) silicon substrates, 752
- Silicon surface**  
 Diamond membranes with controlled porosity, 1824
- SIMS**  
 Lithium addition during CVD diamond deposition using lithium tert.-butanolat as precursor, 494  
 Characterization of electrically active deep level defects in 4H and 6H SiC, 1388
- Si<sub>3</sub>N<sub>4</sub> substrate**  
 Optimization of MW-PACVD diamond deposition parameters for high nucleation density and growth rate on Si<sub>3</sub>N<sub>4</sub> substrate, 411
- Single crystal**  
 Heteroepitaxial diamond growth process on platinum (111), 266  
 Thermal-programmed desorption (TPD) of deuterium from Di(111) surface: presence of two adsorption states, 736  
 The measurement of thermal properties of diamond, 1057
- Single crystals**  
 Diamond growth on a large area and some aspects of diamond nucleation, 426
- Small scale electronic transport**  
 Small scale electronic transport in diamond microcrystals, 325
- Sp<sup>2</sup>**  
 The roles of H and O atoms in diamond growth, 486
- sp<sup>2</sup>/sp<sup>3</sup>-bonded carbon**  
 Quantitative study of Raman scattering and defect optical absorption in CVD diamond films, 704
- sp<sup>3</sup> bonding**  
 Raman diagnostics of amorphous diamond-like carbon films produced with a mass-separated ion beam, 694
- Sp<sup>3</sup> bonding**  
 The roles of H and O atoms in diamond growth, 486
- Space-charge limited current**  
 Electrical properties of PECVD amorphous silicon-carbon alloys from amorphous-crystalline heterojunctions, 1555
- Spectroscopic ellipsometry**  
 Characterization of nucleation and growth of MW-CVD diamond films by spectroscopic ellipsometry and ion beam analysis methods, 1633
- Spectroscopy**  
 Phosphorescence in high-pressure synthetic diamond, 99  
 ESR studies of incorporation of phosphorus into high-pressure synthetic diamond, 356  
 Effects of Mo(CO)<sub>6</sub> and W(CO)<sub>6</sub> introduced to plasma on diamond synthesis by microwave plasma CVD, 501  
 Biased enhanced nucleation of diamond on metals: an OES and electrical investigation, 658  
 Diamond-like hydrogenated amorphous carbon films studied by X-ray emission spectroscopy, 944
- Spin orbit interaction**  
 Valence band dispersion of hexagonal SiC, 1342
- SPM applications**  
 Fabrication of integrated diamond cantilevers with tips for SPM applications, 906
- Sputtering**  
 Characterization and growth of carbon phases synthesized by high temperature carbon ion implantation into copper, 261
- Stacking fault**  
 The origin of 3C polytype inclusions in epitaxial layers of silicon carbide grown by chemical vapour deposition, 1297
- Steel substrate**  
 Adhesion improvement of diamond films on steel substrates using chromium nitride interlayers, 796
- Step-controlled epitaxy**  
 Surface polarity dependence in step-controlled epitaxy: progress in SiC epitaxy, 1276
- Step bunching**  
 Surface polarity dependence in step-controlled epitaxy: progress in SiC epitaxy, 1276
- Step growth**  
 A study on surface morphologies of (001) homoepitaxial diamond films, 130
- Strain**  
 Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807
- Strain relaxation**  
 Optical investigation of thick 3C-SiC layers deposited on bulk silicon by CVD, 1385
- Stress**  
 Stresses generated by inhomogeneous distributions of inclusions in diamonds, 120  
 Free-standing diamond film preparation using copper substrate, 422  
 Phase stability and stress relaxation effects of cubic boron nitride thin films under 350 keV ion irradiation, 621  
 Factors affecting the fracture strength and Young's modulus of CVD diamond-coated fibres, 826  
 Optical properties of diamond film deposited by CVD of Freon: studies on mechanical properties from the absorption band tail, 991  
 Calculation of the stress in large square facets of MPCVD grown diamond from cathodoluminescence and raman spectroscopy measurements and comparison to stress predicted from finite element models, 1062

- Residual strains in GaN grown on 6H-SiC, 1524  
 A study of the initial stages of diamond deposition on ferrous substrates coated by a nitrided chromium interlayer and on nitrided polycrystalline chromium substrates, 1847
- Structural characteristics**  
 Features of diamond deposition on modified silica glass substrates, 444
- Structural defects**  
 Crystalline quality of highly oriented diamond films grown on <100> silicon studied by conventional TEM, 41
- Structural disorder**  
 Insight on the microscopical structure of a-C and a-C:H thin films through electron spin resonance analysis, 725
- Structural properties**  
 Structural properties of GaN grown on SiC substrates by hydride vapor phase epitaxy, 1532
- Structure**  
 Hard a-C(N):H films obtained from plasma decomposition of methylamine-containing mixtures, 631  
 Interfacial analysis of CVD diamond on copper substrates, 743  
 Effect of boron incorporation on the structure of polycrystalline diamond films, 774
- Sublimation**  
 Growth-related structural defects in seeded sublimation-grown SiC, 1272
- Sublimation growth**  
 Sublimation growth of 4H- and 6H-SiC boule crystals, 1262
- Substrate**  
 Structure and properties of a-C:H films deposited onto polymeric substrates, 551  
 Effect of substrate on the characteristics of the interface between diamond film and substrate, 959
- Substrate-stabilized flat-flame**  
 Diamond film deposition by a substrate-stabilized flat flame, 1599
- Substrates**  
 Structural properties of GaN grown on SiC substrates by hydride vapor phase epitaxy, 1532
- Superlattice**  
 Spontaneous radiation in short period superlattices on the basis of carbon multilayer heterostructures, 1106
- Surface**  
 Diamond growth chemistry: its observation using real time in situ molecular beam scattering techniques, 219  
 Surface characterization of smooth heteroepitaxial diamond layers on  $\beta$ -SiC (001), 277  
 Thermal-programmed desorption (TPD) of deuterium from Di(111) surface: presence of two adsorption states, 736  
 Tuning the electron affinity of CVD diamond with adsorbed caesium and oxygen layers, 874
- Surface catalysis**  
 Kinetics of the initial stages of CVD diamond growth on non-diamond substrates: surface catalytic effects and homoepitaxy, 681
- Surface characterization**  
 Investigation of modified 3C SiC(100) surfaces by surface-sensitive techniques, 1353
- Surface diffusion**  
 Low-temperature formation of  $\beta$ -silicon carbide, 645
- Surface energy**  
 Growth of SiC from the liquid phase: wetting and dissolution of SiC, 1266
- Surface morphology**  
 Comparison of the surface structure of carbon films deposited by different methods, 721  
 Comparative investigation of ECR-RIE patterns on Si and C faces of 6H-SiC using a  $\text{CF}_4/\text{O}_2$  gas mixture, 1463
- Surface polarity dependence**  
 Surface polarity dependence in step-controlled epitaxy: progress in SiC epitaxy, 1276
- Surface pretreatment**  
 OBIC studies on 6H-SiC Schottky rectifiers with different surface pretreatments, 1396
- Surface structure**  
 Friction tracks on diamond surfaces imaged by atomic force microscopy, 975  
 Polytypism and surface structure of SiC, 1346  
 Structure and morphology of SiC surfaces studied by LEED, AES, HREELS and STM, 1349
- Surface treatment**  
 Field-emission studies of boron-doped CVD diamond films following surface treatments, 1135
- Synchrotron X-ray photography**  
 Growth-related structural defects in seeded sublimation-grown SiC, 1272
- Synchrotron radiation**  
 Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807  
 Defects formation in sublimation grown 6H-SiC single crystal boules, 1249
- Synthetic diamond**  
 Reactive ion etching of diamond as a means of enhancing chemically-assisted mechanical polishing efficiency, 952  
 Charge carrier trapping centers in synthetic diamond, 1674  
 Observation of micro-inclusions in diamond by scanning X-ray analytical microscope, 1680  
 The formation of diamond from carbonyl material at ambient pressure, 1743  
 Mechanical properties of synthetic type IIa diamond crystal, 1841
- Ta-C:B**  
 Boronated tetrahedral amorphous carbon (ta-C:B), 207
- Tafel polarization**  
 Electrochemical characterization of doped and undoped CVD diamond deposited by microwave plasma, 17
- TEM**  
 TEM investigations on the heteroepitaxial nucleation of CVD diamond on (001) silicon substrates, 752  
 Investigation of the boron incorporation in polycrystalline CVD diamond films by TEM, EELS and Raman spectroscopy, 763  
 Optical study of boron nitride thin films prepared by plasma-enhanced chemical vapor deposition, 1550
- Temperature**  
 Thermal resistance and electrical insulation of thin low-temperature-deposited diamond films, 298  
 The characterization of single structure diamond heater and temperature sensor, 394  
 High field/high temperature performance of semi-insulating silicon carbide, 1392
- Temperature dependance**  
 Temperature dependence of electrical properties of 6H-SiC buried gate JFET, 1504
- Temperatures**  
 Charge carrier trapping centers in synthetic diamond, 1674
- Termination**  
 2.5 kV ion-implanted  $p^+n$  diodes in 6H-SiC, 1485
- Tetrahedral amorphous carbon**  
 Paramagnetic centres in tetrahedral amorphous carbon, 783  
 Electronic and atomic structure of undoped and doped ta-C films, 830  
 Optical and electrical characteristics of amorphous diamond films, 983

- Tetrahedral amorphous carbon (ta-C) coatings for processing tools to reduce contamination in the analysis of trace elements, 1207
- Ion beam modification of tetrahedral amorphous carbon: the effect of irradiation temperature, 1622
- Texture**
- Cathodoluminescence spectroscopy of synthetic diamond films, 717
  - Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807
  - Diamond fibres by a hot filament CVD process, 822
  - On the {111} penetration twin density in CVD diamond films, 1697
- [100]-texture
- [100]-Textured diamond films for tribological applications, 381
- Theory**
- Polytypism and surface structure of SiC, 1346
- Thermal annealing**
- Effects of thermal and laser annealing on silicon carbide nanopowder produced in radio frequency glow discharge, 1559
- Thermal conductivity**
- The measurement of thermal properties of diamond, 1057
  - Thermal properties of  $\beta$ -SiC epitaxial layers between 150 C and 500 C measured by using microstructures, 1338
- Thermal effusion**
- Thermal gas effusion from diamond-like carbon films, 1830
- Thermal energy**
- Etching of graphite and diamond by thermal energy hydrogen atoms, 787
- Thermal management**
- Design-to-implementation case studies of CVD diamond in r.f./microwave package and detector applications, 191
- Thermal oxidation**
- Fabrication of high-quality oxides on SiC by remote PECVD, 1420
  - Anisotropic oxidation of silicon carbide, 1467
- Thermal properties**
- Measurement and calculation of the thermal expansion coefficient of diamond, 839
- Thermal resistance**
- Thermal resistance and electrical insulation of thin low-temperature-deposited diamond films, 298
- Thermal stability**
- Electrical properties and thermal stability of ion beam deposited BN thin films, 1129
  - Radiation-induced defect centers in 4H silicon carbide, 1333
- Thermodynamic perturbation theory**
- Thermodynamic properties of  $^{13}\text{C}$ -diamond, 172
- Thermodynamic properties**
- Thermodynamic properties of  $^{13}\text{C}$ -diamond, 172
- Thermodynamics**
- Thermodynamics and high-pressure growth of (Al, Ga, In)N single crystals, 1515
- Thin CVD diamond films**
- HREM and EXELFS investigation of local structure in thin CVD diamond films, 758
- Thin film field emitters**
- Internal field emission at metal/diamond contact and performance of thin film field emitters: computer simulation, 884
- Thin films**
- Nonlinear optical mapping of 3C-inclusions in 6H-SiC-epilayers, 1374
- Three-dimensional substrates**
- Experimental and theoretical studies of growth mechanisms of hard wear-resistant carbon-based films on three-dimensional substrates, 970
- Thyristors**
- SiC device technology: remaining issues, 1400
- Ti-6Al-4V**
- Residual stress in polycrystalline diamond/Ti-6Al-4V systems, 807
- Time delay**
- Transient nucleation of diamond: theoretical and experimental study, 1092
- Titanium**
- Stiffness, residual stresses and interfacial fracture energy of diamond films on titanium, 1612
- Titanium alloy**
- Growth stages of chemical vapor deposited diamond on the titanium alloy Ti-6Al-4V, 1658
- Topography**
- Wafer warpage, crystal bending and interface properties of 4H-SiC epi-wafers, 1369
- Transient behaviour**
- Electron field emission from thin fine-grained CVD diamond films, 1111
- Transient kinetics**
- Transient nucleation of diamond: theoretical and experimental study, 1092
- Transmission electron microscopy**
- Transmission electron microscope study of heteroepitaxial diamond on Pt (111), 272
  - The influence of boron doping on the structure and characteristics of diamond thin films, 521
  - Microstructure and growth of MWCVD diamond on  $\text{Si}_{1-x}\text{C}_x$  buffer layers, 649
  - Interfacial analysis of CVD diamond on copper substrates, 743
  - Aluminium implantation of  $p$ -SiC for ohmic contacts, 1414
  - Anisotropic oxidation of silicon carbide, 1467
- Transmission electron microscopy (TEM)**
- The origin of 3C polytype inclusions in epitaxial layers of silicon carbide grown by chemical vapour deposition, 1297
- Transport mechanisms**
- Electrical properties of PECVD amorphous silicon-carbon alloys from amorphous-crystalline heterojunctions, 1555
- Tribology**
- [100]-Textured diamond films for tribological applications, 381
- Tubes**
- Cylindrically symmetric diamond parts by hot-filament CVD, 1707
- Tungsten Carbide**
- Ion beam assisted deposition of a tungsten compound layer on 6H-silicon carbide, 1432
- Twinning**
- On the development of CVD diamond film morphology due to the twinning on {111} surfaces, 435
  - On the {111} penetration twin density in CVD diamond films, 1697
- Two-dimensional symmetry**
- Cylindrically symmetric diamond parts by hot-filament CVD, 1707
- Type Ib diamond**
- The 0.545 eV center in neutron irradiated and annealed type Ib diamond, 1722
- UHV**
- a-SiC:H films deposited by PECVD from silane + acetylene and silane + acetylene + hydrogen gas mixture, 1606

- Ultrafine diamond**
- Diamond seed incorporation by electrochemical treatment of silicon substrate, 1629
- Ultrasonic vibration**
- The effect of ultrasonic vibration on CVD diamond nucleation, 1031
- UV range**
- Electrical conduction in polycrystalline diamond and the effects of UV irradiation, 860
- Vacancy complexes**
- Deep luminescent centres in electron-irradiated 6H SiC, 1378
- Vibrational spectroscopy**
- Investigation of modified 3C SiC(100) surfaces by surface-sensitive techniques, 1353
- Walk-out**
- Investigation of walk-out phenomena in SiC mesa diodes with  $\text{SiO}_2/\text{Si}_3\text{N}_4$  passivation, 1476
- Water-jet**
- Cylindrically symmetric diamond parts by hot-filament CVD, 1707
- WC-Co surfaces**
- High quality diamond films on WC-Co surfaces, 89
- Wear**
- Microtribological properties of diamond-like and hydrogenated carbon coatings grown by different methods, 1
  - Evaluation of diamond-like carbon-coated orthopaedic implants, 390
  - Tetrahedral amorphous carbon (ta-C) coatings for processing tools to reduce contamination in the analysis of trace elements, 1207
- Wettability**
- Diamond formation and wettability in a Mg–Cu–C system under high pressure and high temperature, 28
  - Formation peculiarities of the interfacial structure during cBN wetting with Ag–Ti, Ag–Zr and Ag–Hf alloys, 931
- Wetting**
- Growth of SiC from the liquid phase: wetting and dissolution of SiC, 1266
- Wide band gap semiconductors**
- The potential of SiC and GaN for application in high speed devices, 1512
- Work function**
- An interface study of vapor-deposited rhenium with the two (0001) polar faces of single crystal 6H-SiC, 1424
- Wurtzite boron nitride**
- In-situ X-ray observation of phase transformation of rhombohedral boron nitride under static high pressure and high temperature, 1806
- X-ray**
- Lift-off technique of homoepitaxial CVD diamond films by deep implantation and selective etching, 654
  - Effect of boron incorporation on the structure of polycrystalline diamond films, 774
- Diamond-like hydrogenated amorphous carbon films studied by X-ray emission spectroscopy, 944**
- Capabilities of combined studies of DLC films by X-ray methods, 1784**
- X-Ray absorption**
- Identification of the cubic and hexagonal polytypes of GaN with X-ray absorption measurements, 1539
- X-ray detector**
- Growth and characterisation of CVD diamond wires for X-ray detection, 1051
- X-ray diffraction**
- Residual stress in polycrystalline diamond/Ti–6Al–4V systems, 807
  - Growth of AlN thin films on (111) and (100) silicon by pulsed laser deposition in nitrogen plasma ambient, 1015
  - Wafer warpage, crystal bending and interface properties of 4H-SiC epi-wafers, 1369
- X-ray microradiography**
- Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226
  - Low frequency noise in silicon carbide Schottky diodes, 1494
  - Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- X-ray mirrors**
- Use of diamond-like carbon films in X-ray optics, 902
- X-ray optics**
- Use of diamond-like carbon films in X-ray optics, 902
- X-ray photoelectron diffraction**
- Formation of an oriented  $\beta$ -SiC layer during the initial growth phase of diamond on silicon (100), 282
- X-ray photoelectron spectroscopy**
- An interface study of vapor-deposited rhenium with the two (0001) polar faces of single crystal 6H-SiC, 1424
- X-ray topography**
- Combining optical microscopy, X-ray microradiography and X-ray topography in the study of individual CVD diamond crystallites, 1226
  - Low frequency noise in silicon carbide Schottky diodes, 1494
  - Surface and bulk effects in ex-situ hydrogenated  $\alpha$ -SiC thin films, 1547
- Young's modulus**
- High temperature Young's modulus of polycrystalline diamond, 344
  - Elastic properties of polycrystalline cubic boron nitride and diamond by dynamic resonance measurements, 812
  - The effect of varying deposition conditions on the Young's modulus of diamond coated wires, 817
  - Factors affecting the fracture strength and Young's modulus of CVD diamond-coated fibres, 826
  - CBN– $\text{TiH}_2$  composites: chemical equilibria, microstructure and mechanical studies, 1192
- Zincblend type cubic boron nitride**
- In-situ X-ray observation of phase transformation of rhombohedral boron nitride under static high pressure and high temperature, 1806

